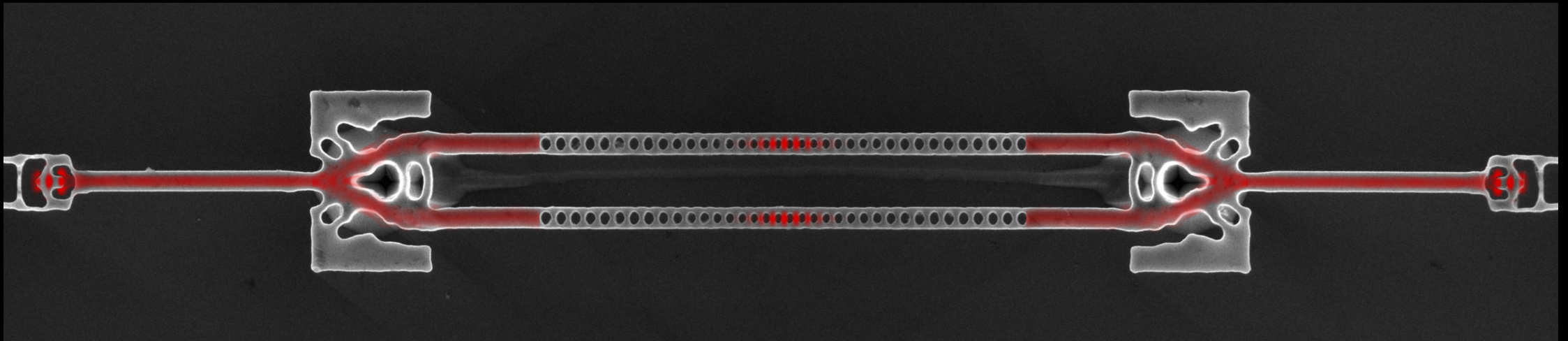
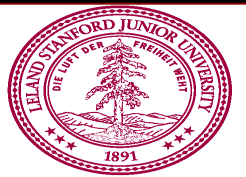


Connecting and scaling semiconductor quantum photonic systems



Jelena Vuckovic

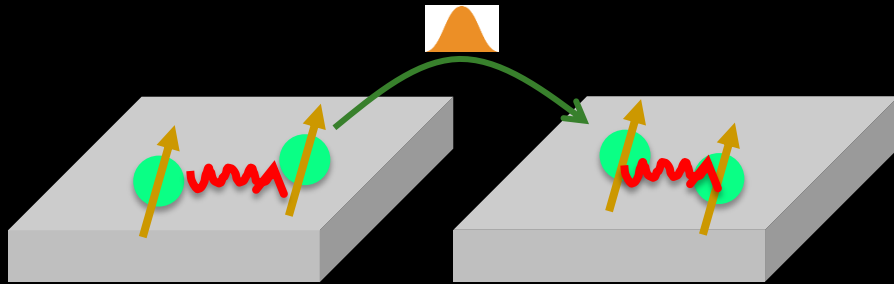


Stanford University

Photonics for Quantum 2, June 2020

Quantum technologies

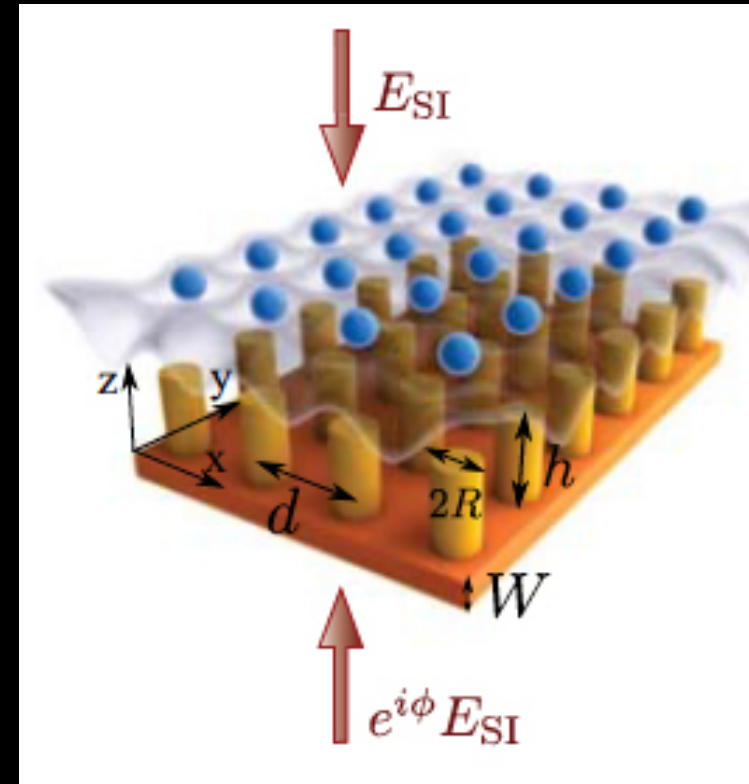
Quantum repeaters and networks



What do we need?

- 1) Homogeneous, long lived qubits with (optical) interfaces
- 2) Efficient optical interconnects

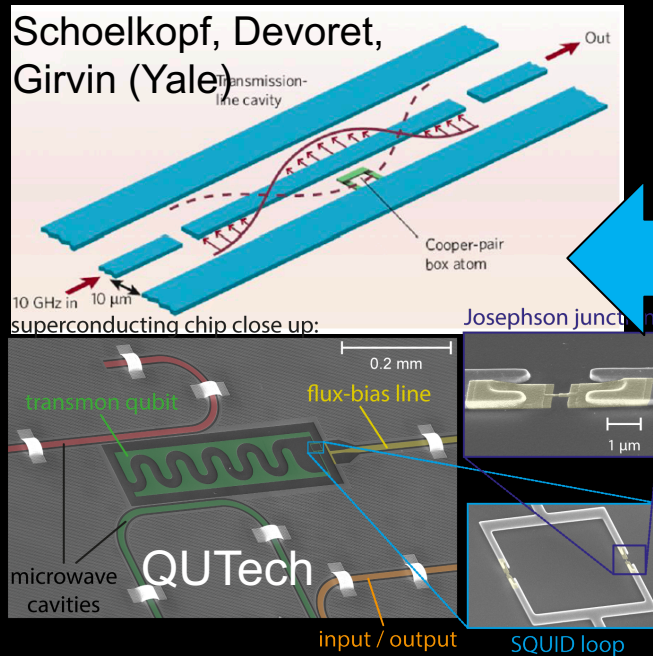
Quantum simulators & computers



Gonzales-Tudela et al., *Nature Photonics* 9, 320-325 (2015).
Douglas et al., *Nature Photonics* 9, 326-331 (2015).

Optically interfaced semiconductor spin qubits

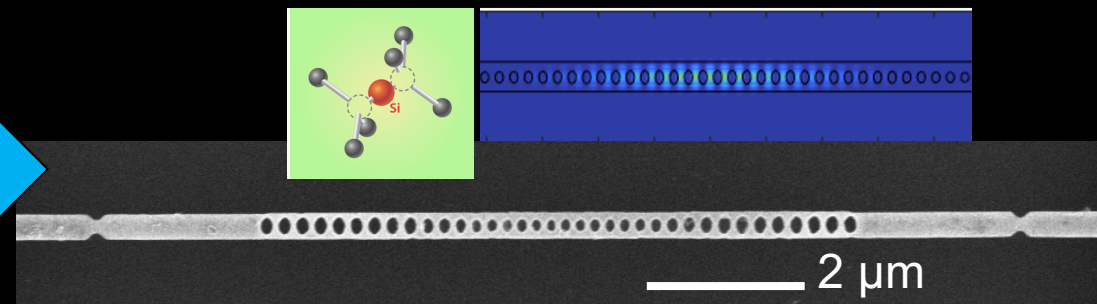
Superconducting qubit in a microwave cavity



- Large, traditional microfab => easy to make them all the same
- Superconductors
- Microwave frequencies
- No direct optical interface

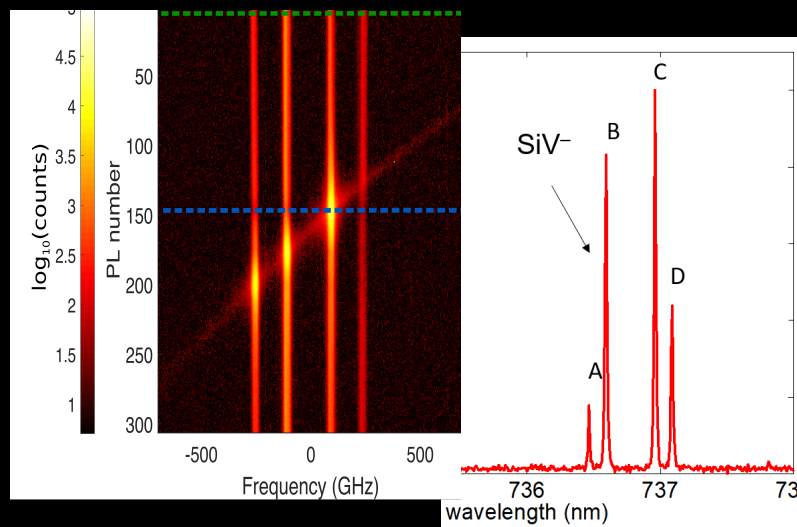
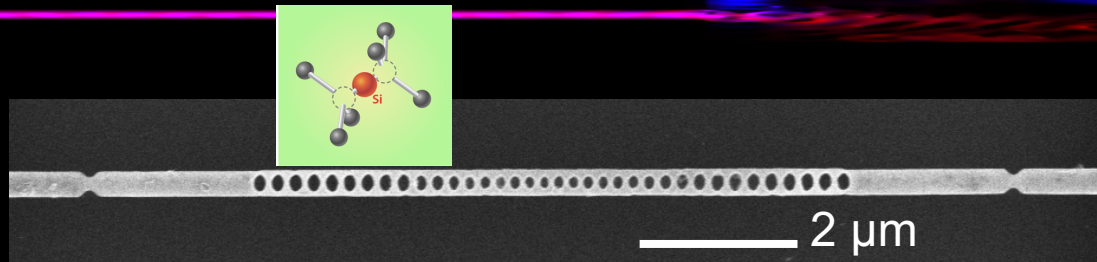
(Artificial) atom in an optical cavity

Color centers in diamond and silicon carbide

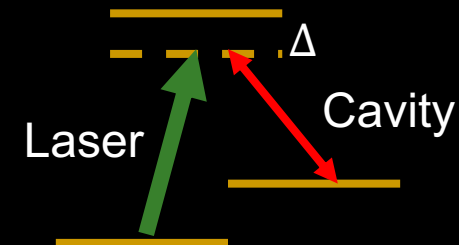
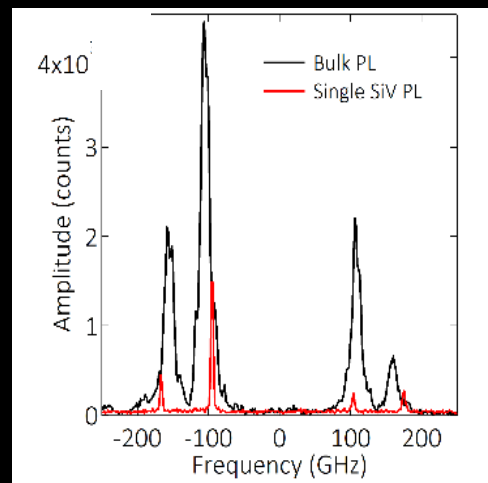


- Smaller by >1000x => nanofabrication + ion implantation/CVD (more challenging to make them all the same)
- Semiconductors
- Possibility of operation at higher temperatures (~2-10K)
- Excellent photon interface
- Number of 2-qubit gate operations per electron spin qubit coherence time > superconducting qubits

SiV color centers in diamond



Only 30GHz spectral broadening for SiVs on chip



Excellent photonic interface for SiV

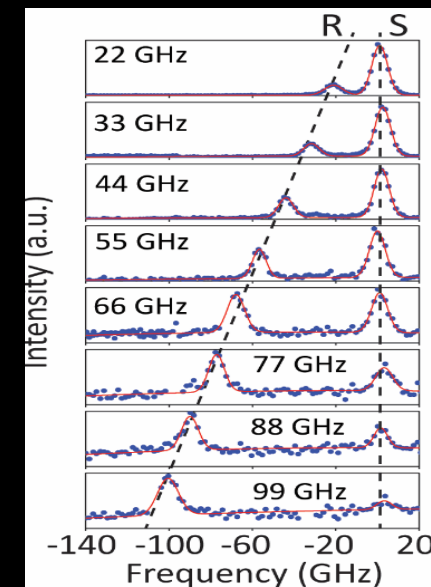
Nano Lett., 18 (2), pp 1360–1365 (2018)

2 qubit interaction (Harvard)

Science 362, 662-665 (2018)

Collaborators: @ Stanford: Melosh, Safavi-Naeini. @ Harvard: Loncar

Jelena Vuckovic, Stanford



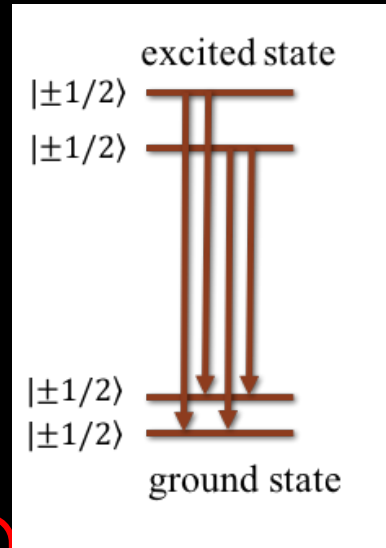
Can couple SiVs on chip detuned by 100GHz by Raman scattering

Phys. Rev. Letters 121, 083601 (2018)

New inversion symmetric diamond color centers

6 C Carbon 12.011
14 Si Silicon 28.085
32 Ge Germanium 72.630
50 Sn Tin 118.71
82 Pb Lead 207.2
114 Fl Flerovium (289)

	Ground state splitting	Debye–Waller factor	Quantum efficiency
SiV⁻	50 GHz [1]	78% [6]	30% [8], 14% *[5]
GeV⁻	152 GHz [2]	61% [7]	90% *[5]
SnV⁻	850 GHz [3]	41% [3]	80% [3], 91% *[5]
PbV⁻	2 THz [4] 4.4 THz *[5]	20% *[5]	unknown



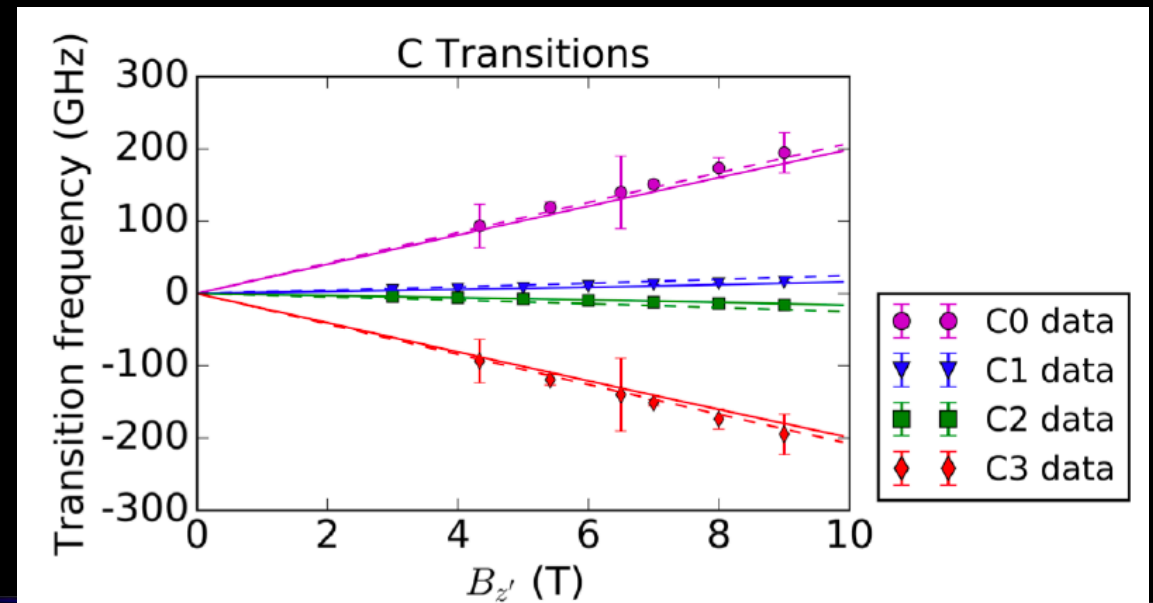
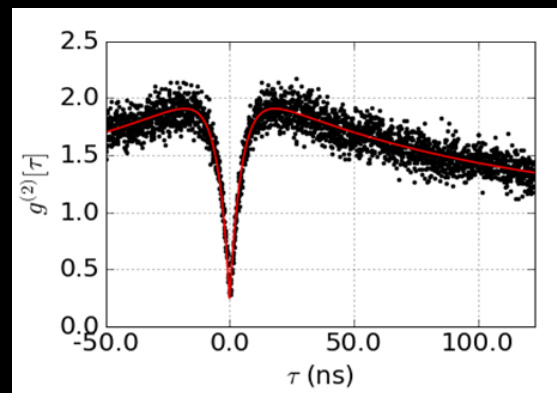
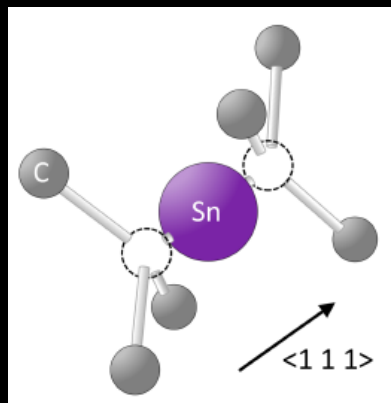
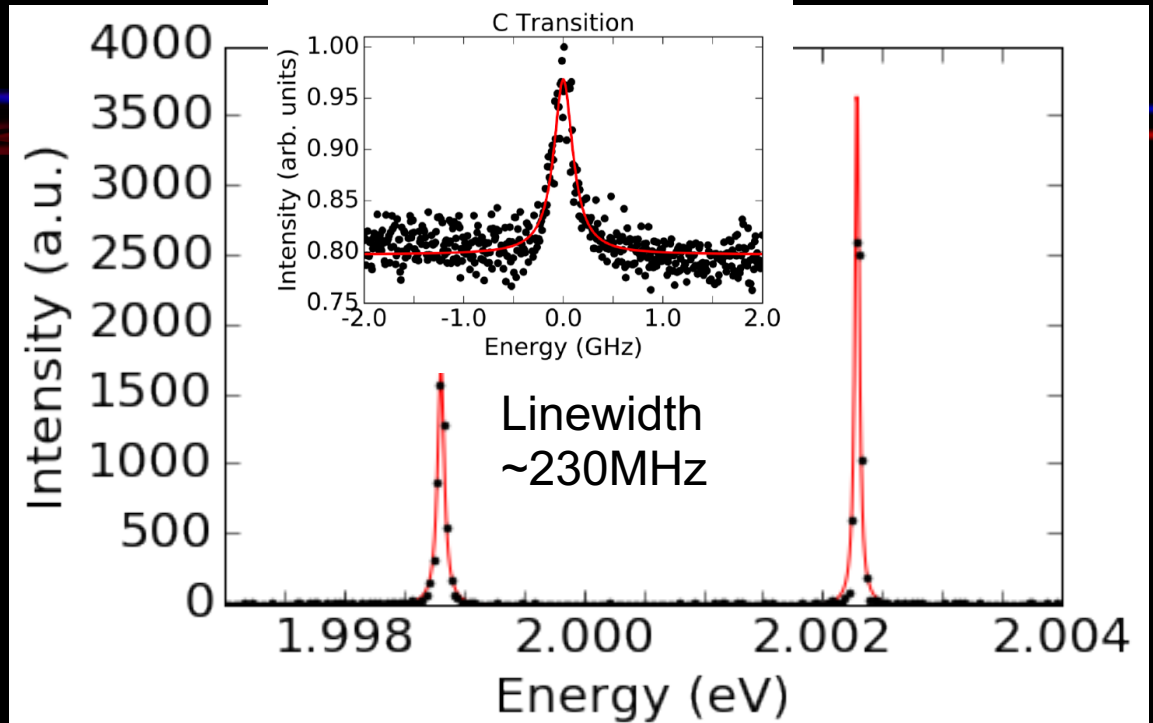
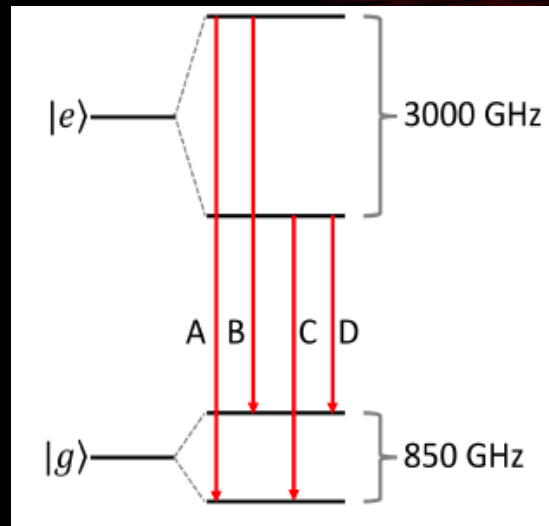
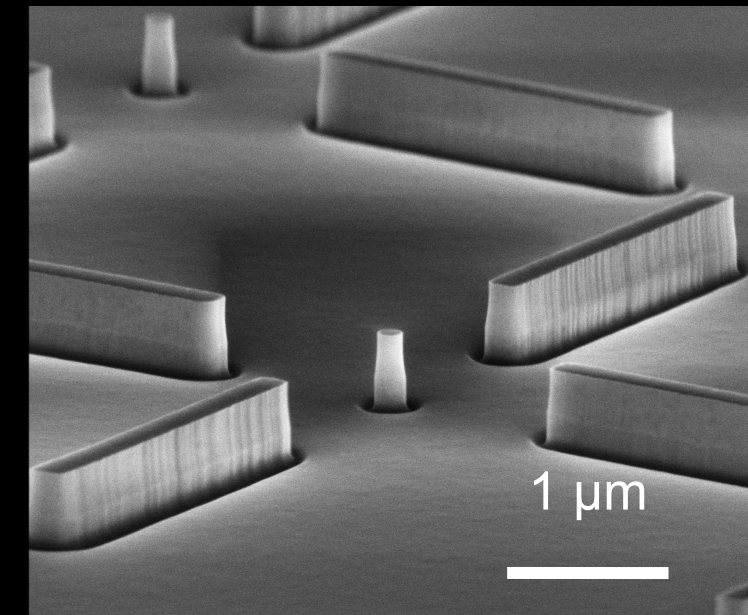
* Based on *ab initio* calculations

**SnV color centers:
elevated
temperatures (~2K)
+ much higher
efficiency than SiV**

- [1] Hepp et al., *Phys. Rev. Lett.* 112, 036405 (2014)
 [2] Bhaskar et al., *Phys. Rev. Lett.* 118, 223603 (2017)
 [3] Iwasaki et al., *Phys. Rev. Lett.* 119, 253601 (2017)
 [4] Trusheim et al., arXiv:1805.12202
 [5] Thiering and Gali, *Phys. Rev. X* 8, 021063 (2018)

- [6] Neu et al., *New J. Phys.* 13, 025012 (2011)
 [7] Palyanov et al., *Sci. Rep.* 5, 14789 (2015)
 [8] Becker and Becher, *Phys. Status Solidi A* 214, 1700586 (2017)

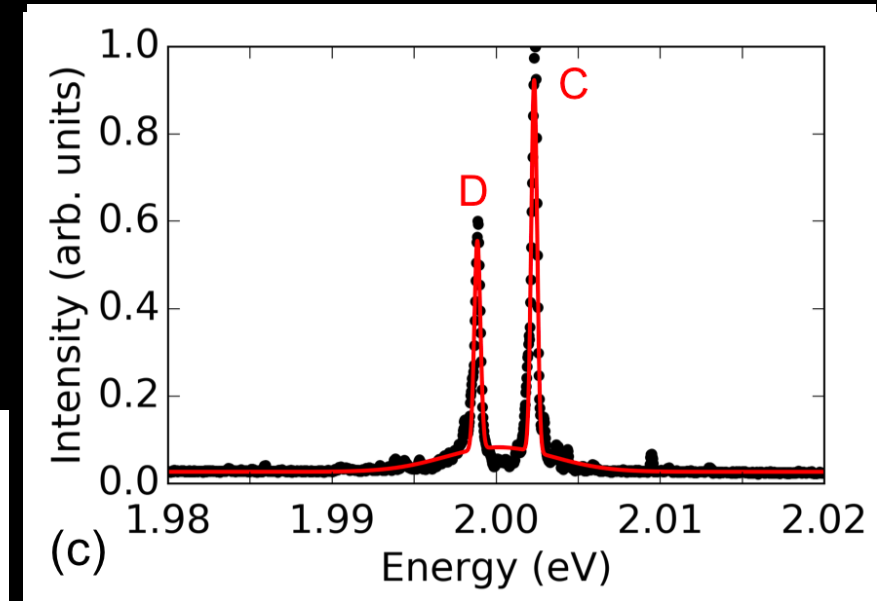
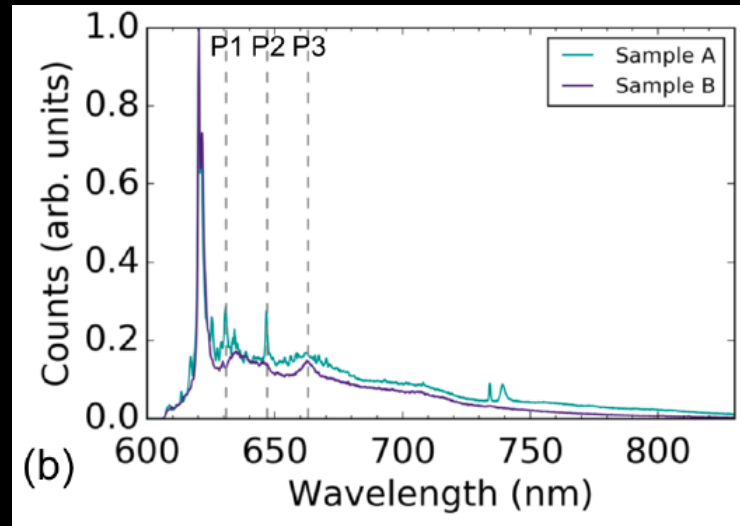
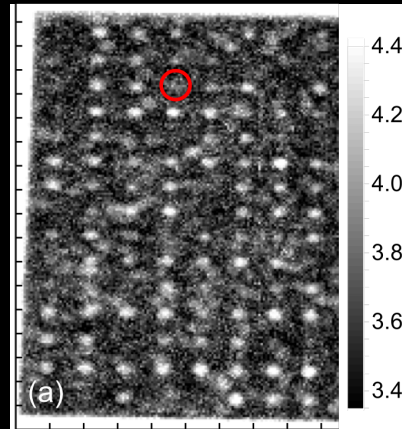
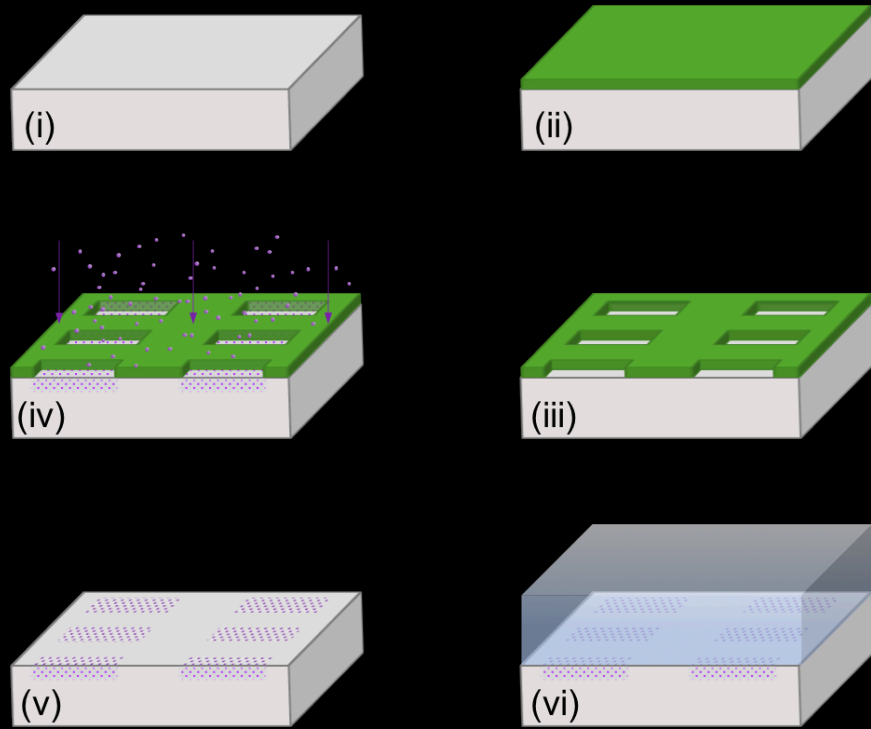
Characterization of single SnV's



A. Rugar, et al., *Phys. Rev. B* 99, 205417 (2019)

Similar work: Trusheim et al., *PRL* 124, 023602 (2020)

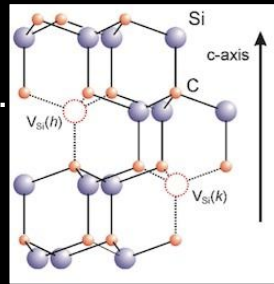
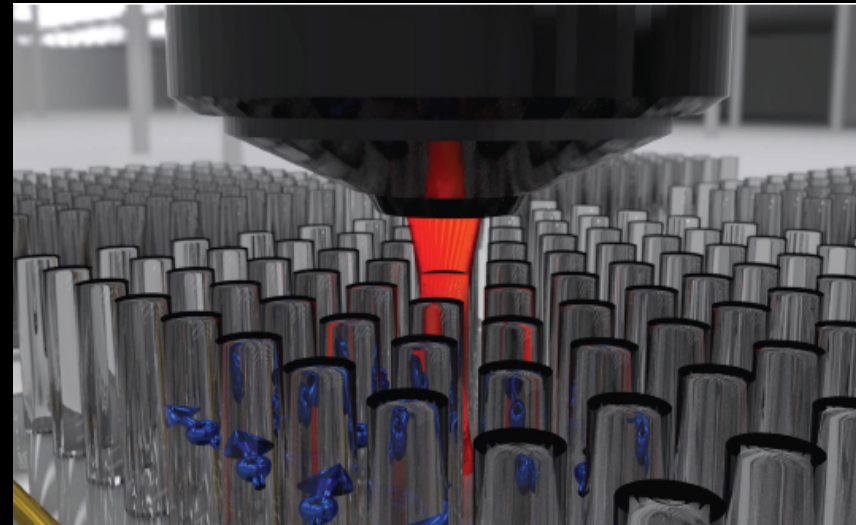
SnV in Diamond via Shallow Ion Implantation and Subsequent Diamond Overgrowth



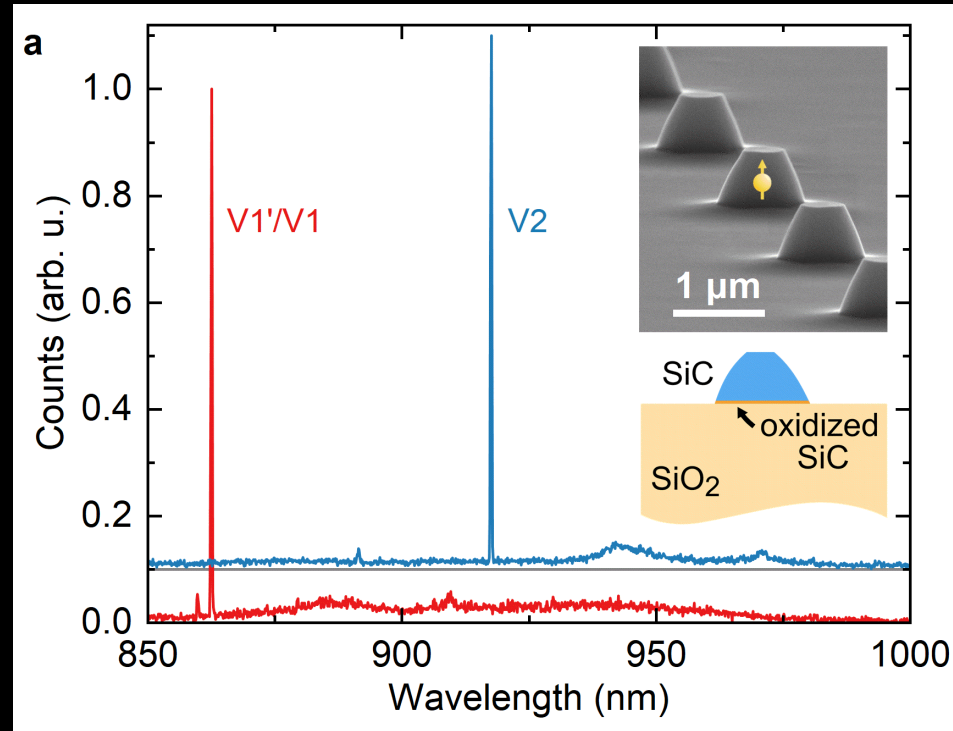
Sample A: 370keV implantation
Sample B: 1keV implantation

A. Rugar et al, *Nano Letters* **20**, pp. 1614-1619 (2020)

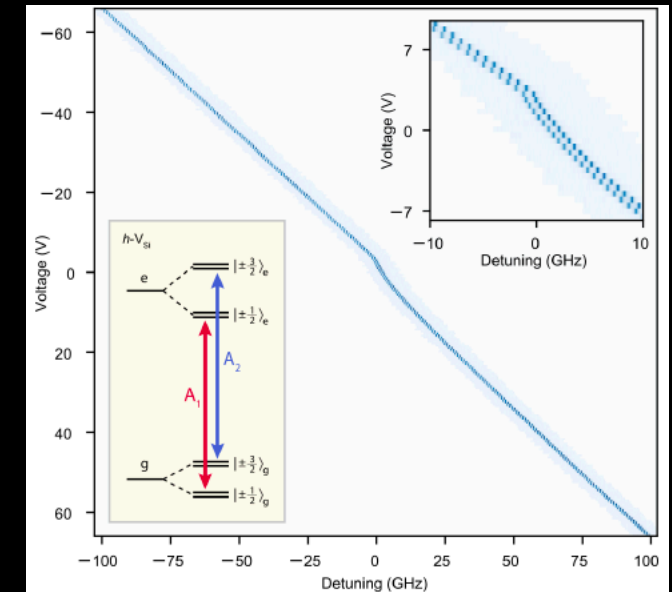
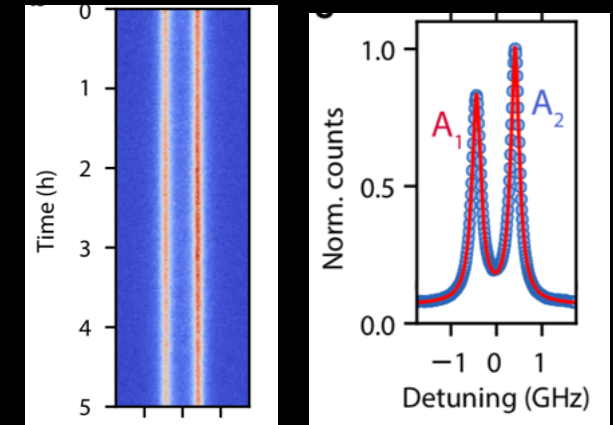
V_{Si} in 4H-SiC



- collaboration with J. Wrachtrup (Stuttgart) & S. Economou (VTech)
- e-spin coherence time ~ 20 ms
- Indistinguishable photons generated
- 65 MHz transitions (lifetime limit 35 MHz)



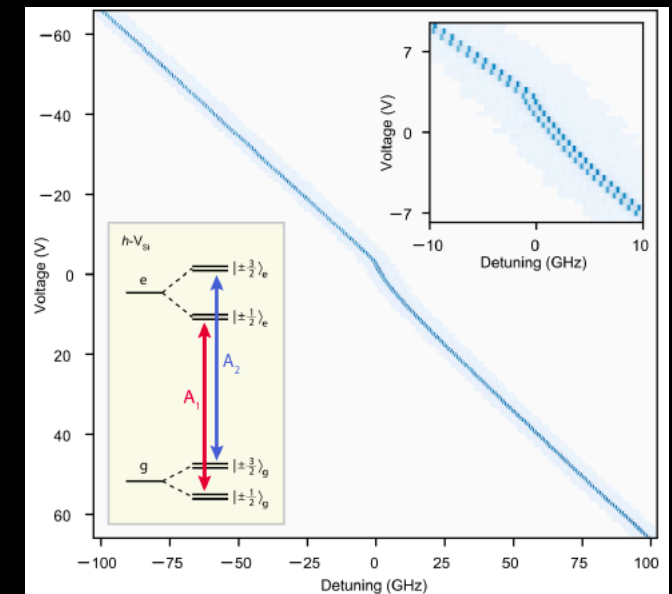
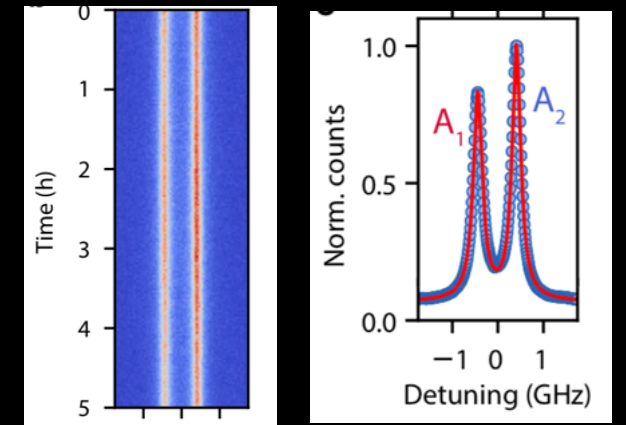
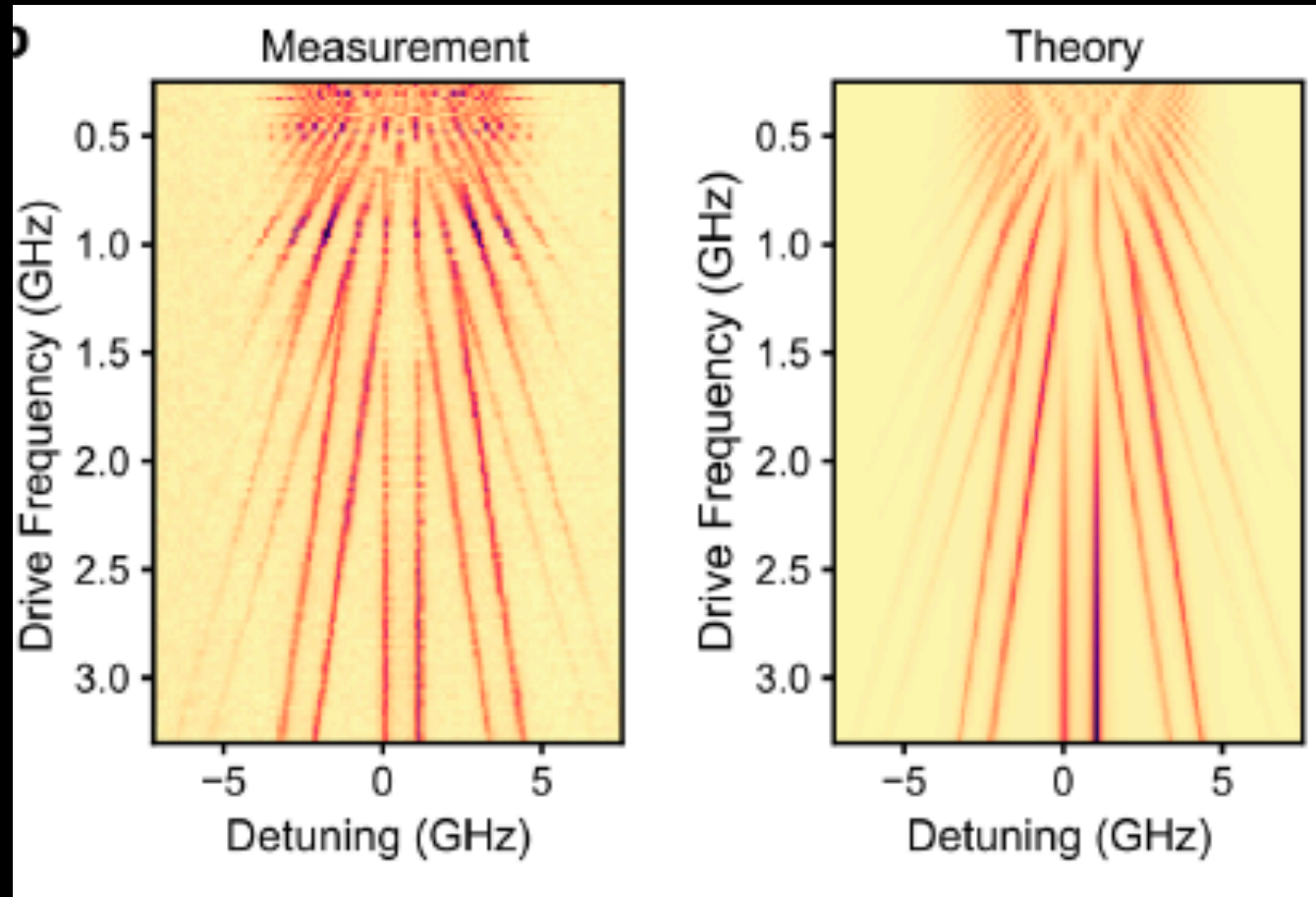
- Very stable transitions
- DC Stark tuning to compensate full inhomogeneous broadening



Nano Letters **17**, 3, 1782-1786 (2017)
Physical Review Applied, **9**, 034022 (2018)
Nature Photonics vol. **14**, pp. 330-334 (2020)

[arXiv:2003.12591]

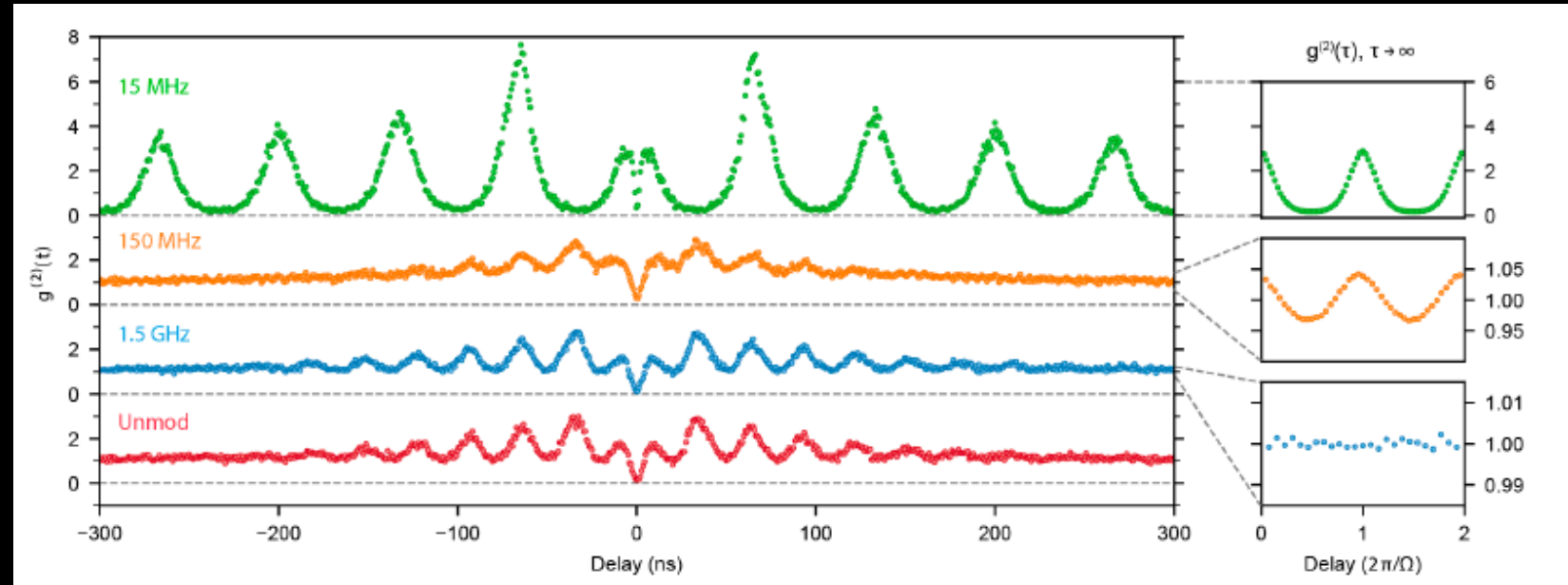
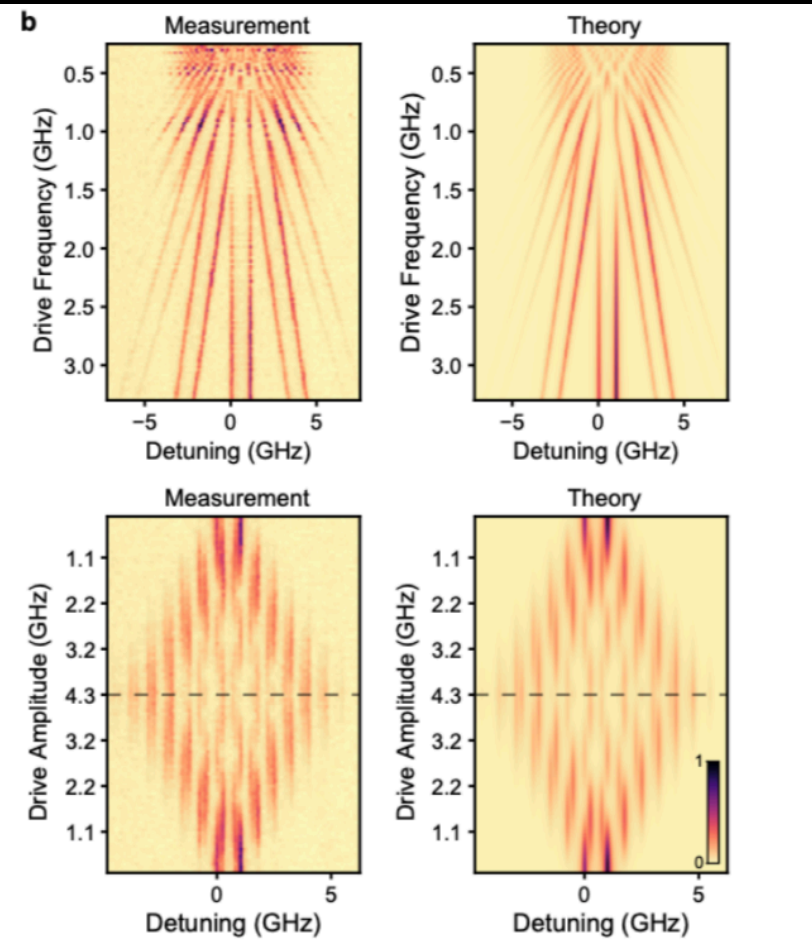
Floquet eigenstates



D. Lukin, A. White, M. Guidry, R. Trivedi et al [arXiv:2003.12591]

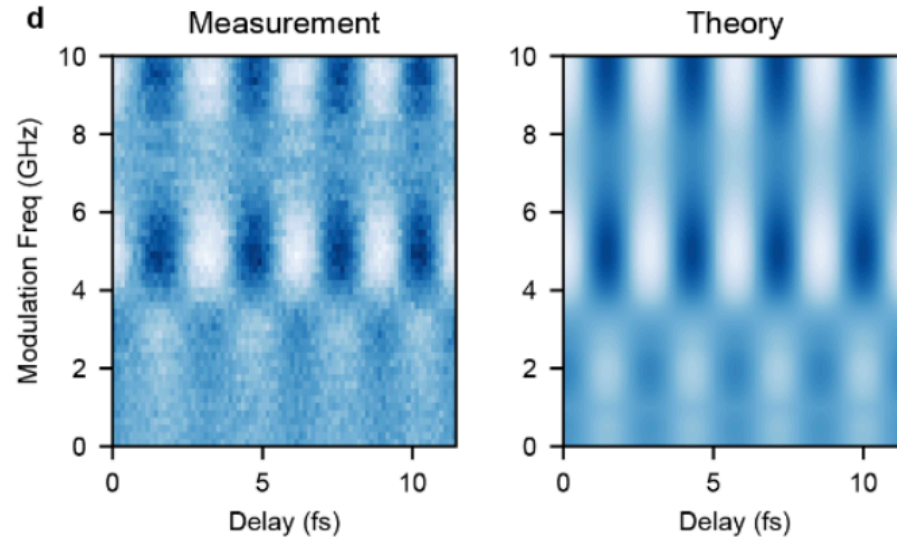
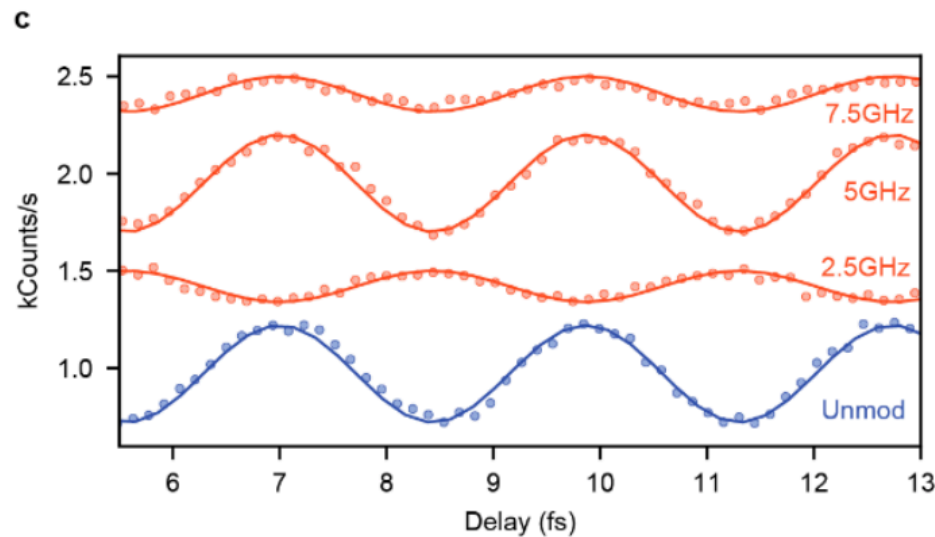
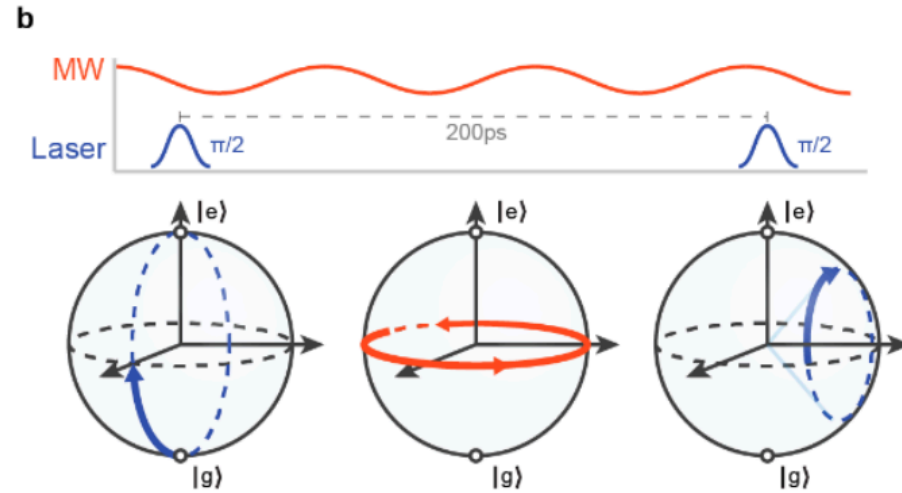
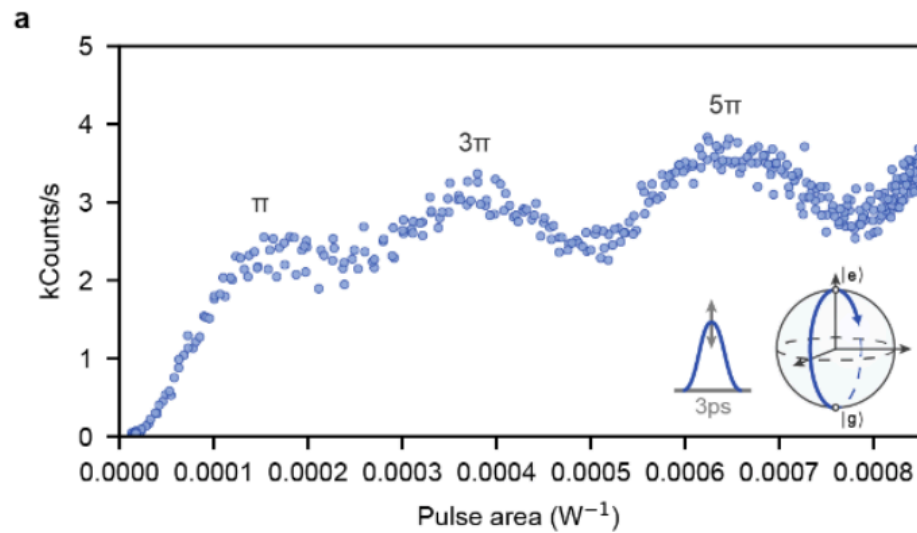
VSi in SiC

Photon statistics

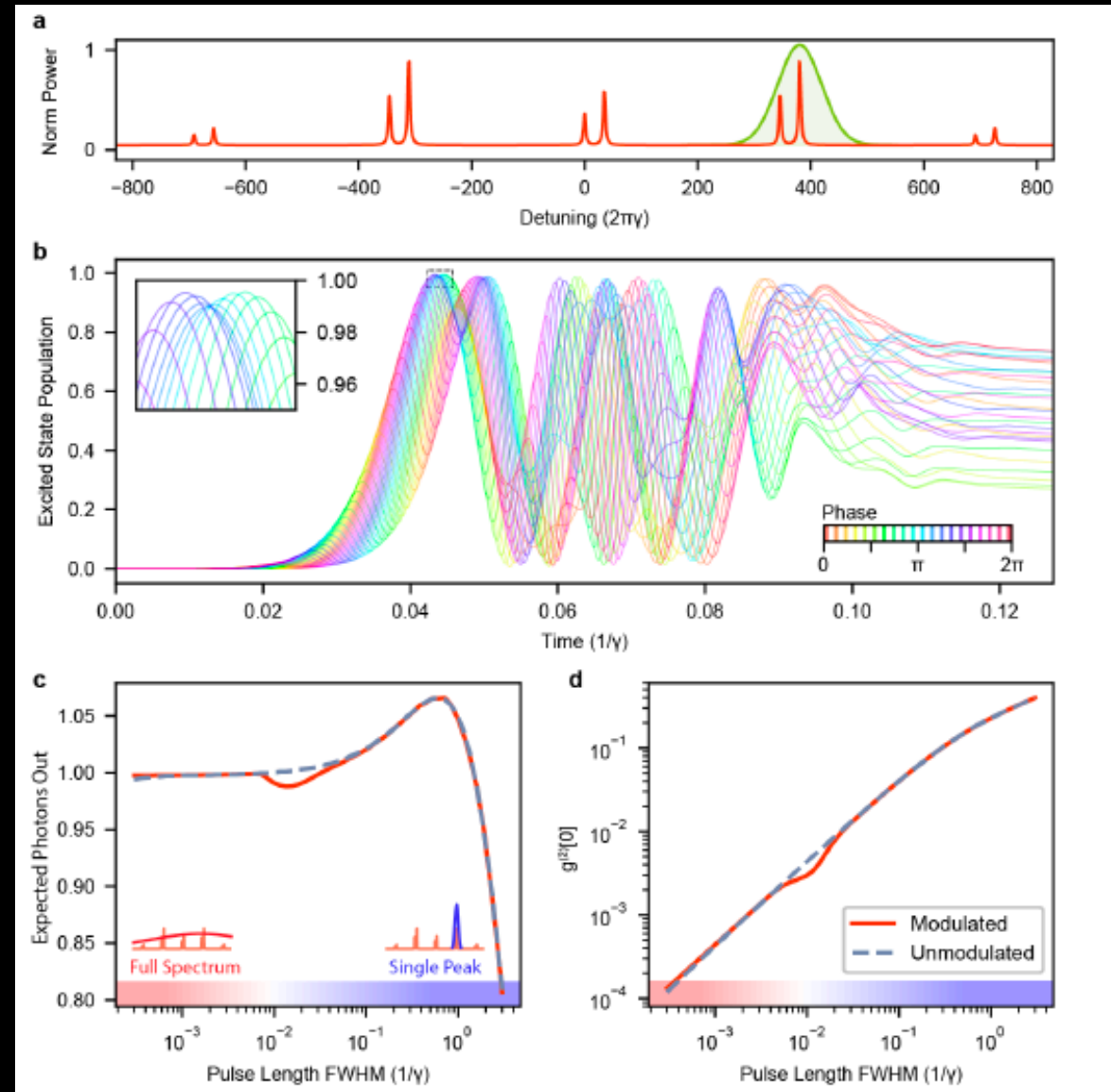


D. Lukin, A. White, M. Guidry, R. Trivedi et al [*arXiv:2003.12591*]

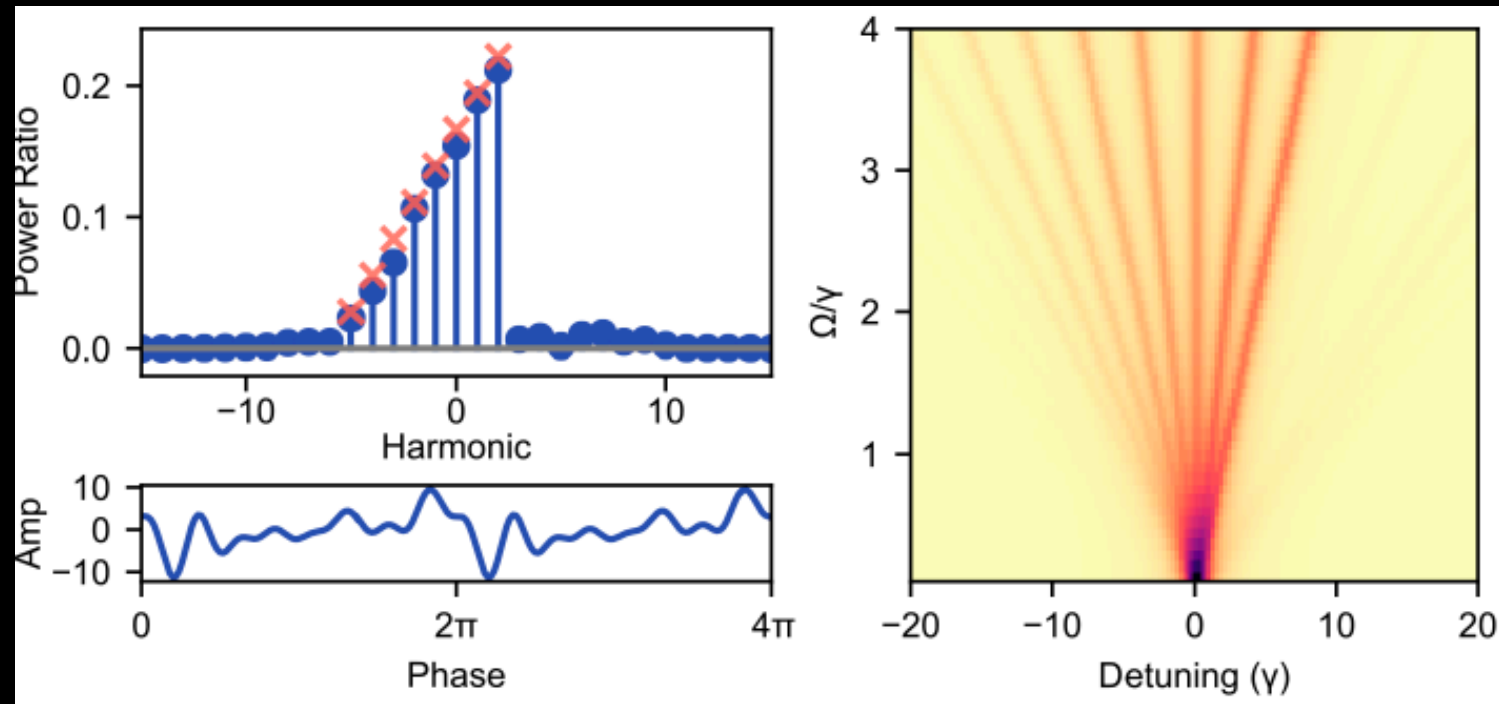
Pulsed optical coherent control of a modulated single emitter



Shaped single photon emission by pulsed modulation



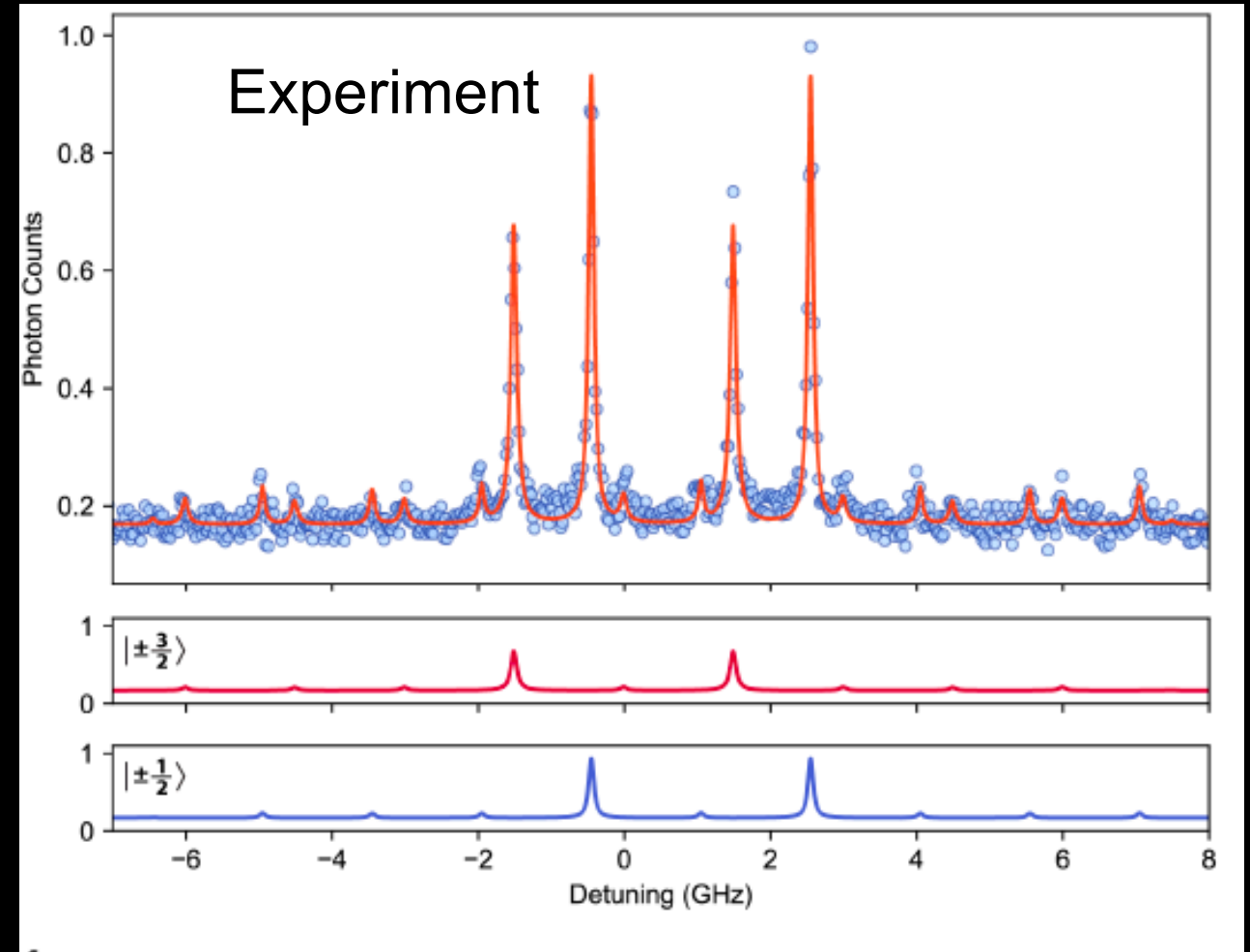
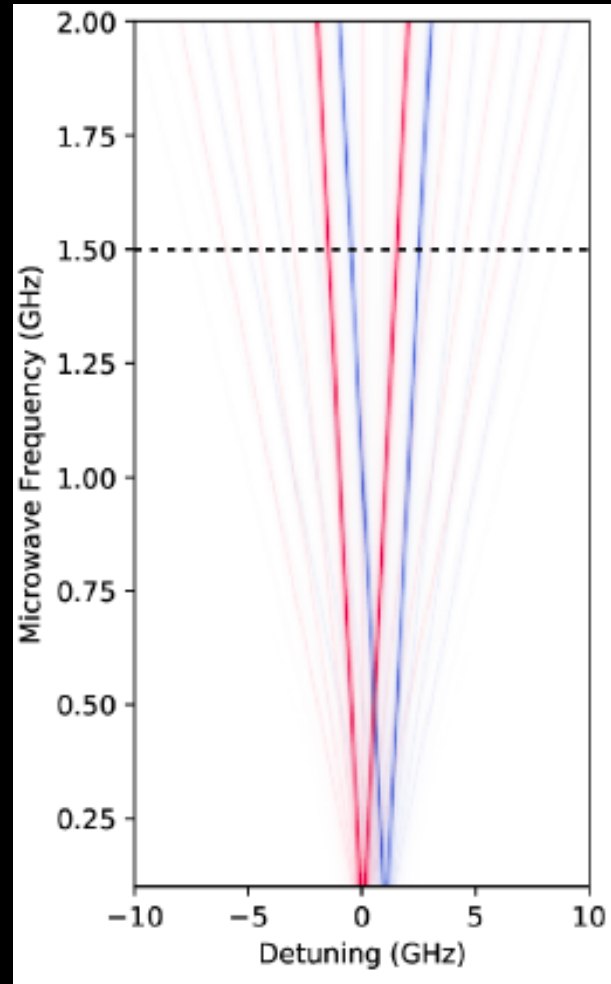
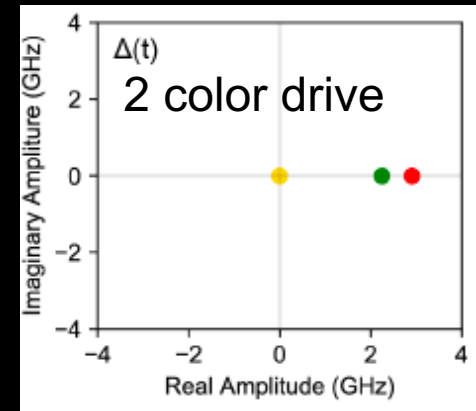
Spectrally reconfigurable quantum emitters enabled by optimized fast modulation



D. Lukin, A. White, M. Guidry, R. Trivedi et al [*arXiv:2003.12591*]

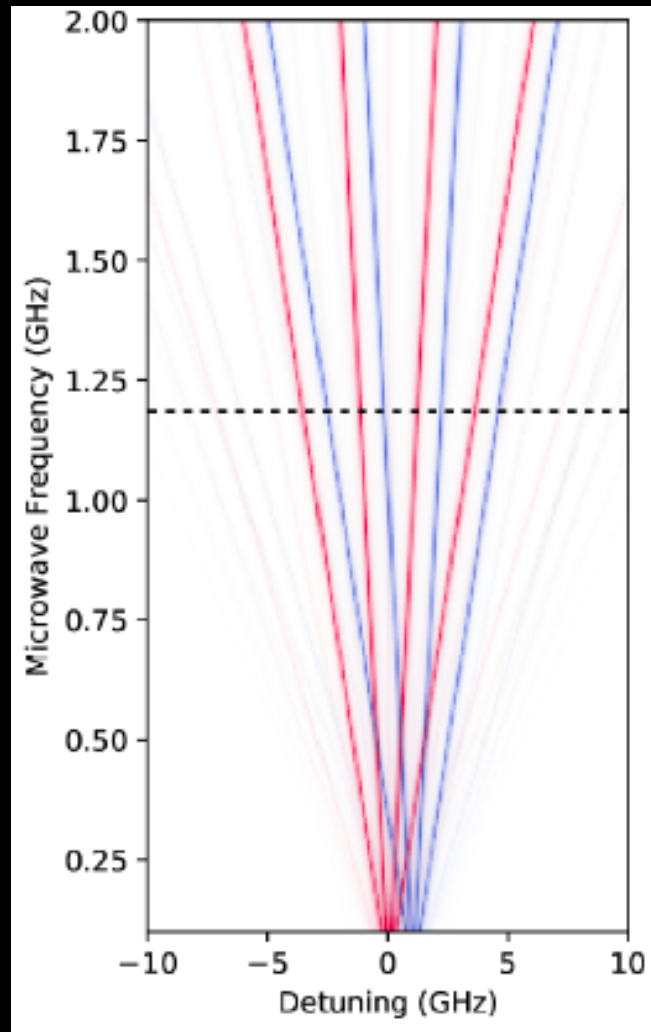
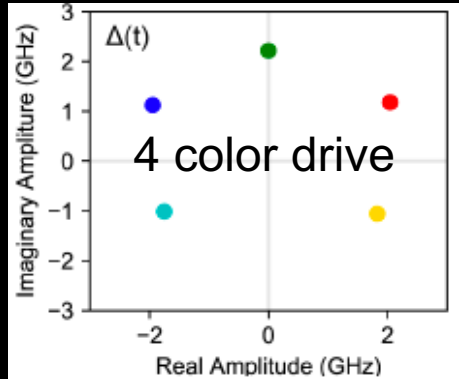
Spectrally reconfigurable quantum emitters enabled by optimized fast modulation

theory

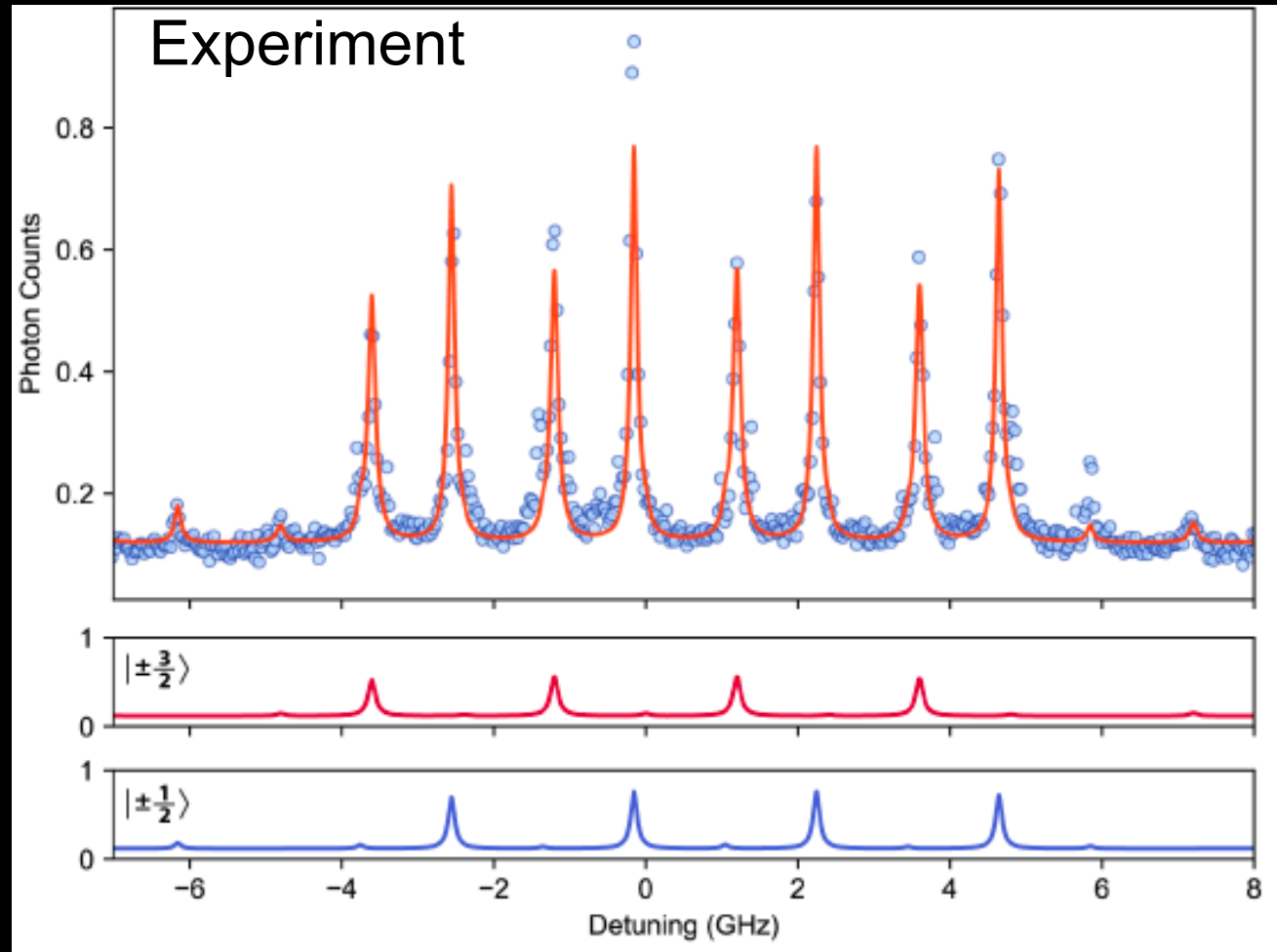


Spectrally reconfigurable quantum emitters enabled by optimized fast modulation

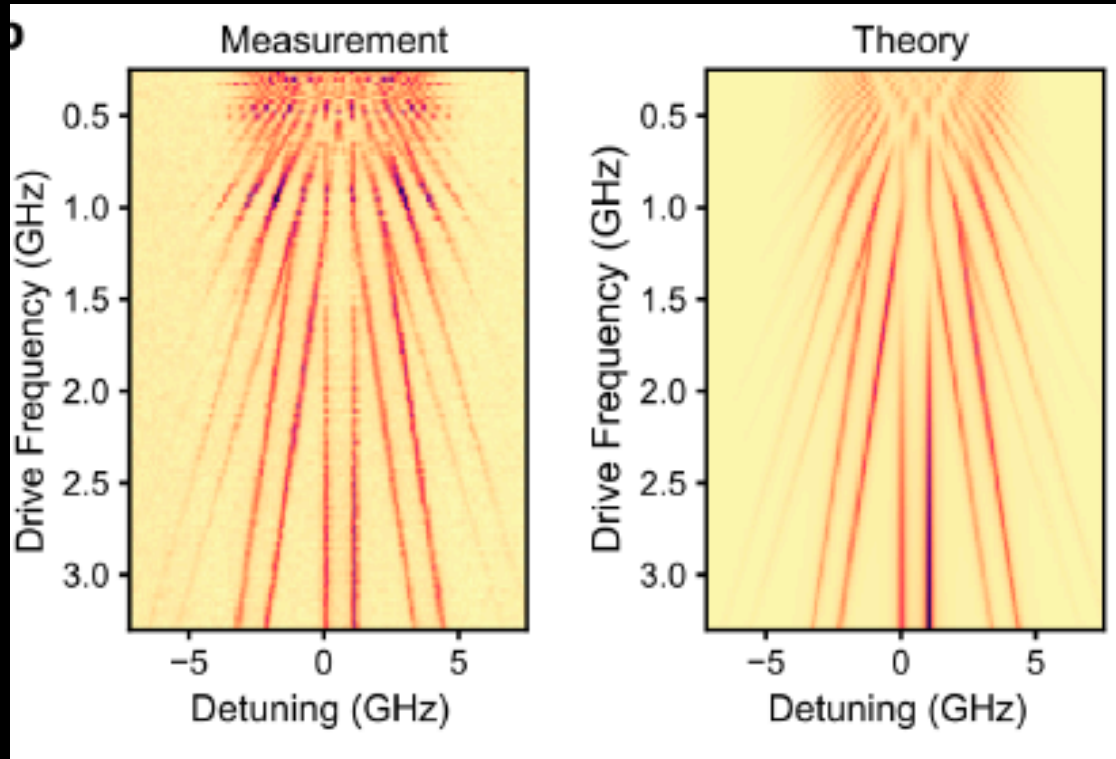
theory



Experiment



Floquet engineering for removing emitter inhomogeneity



Controllably pulsing a Hamiltonian with inhomogeneously broadened spins.

$$H = \sum_i \frac{\omega_i}{2} \sigma_z^i + \sum_i J [\alpha(t) \sigma_+^i \sigma_-^{i+1} + \text{h.c.}]$$



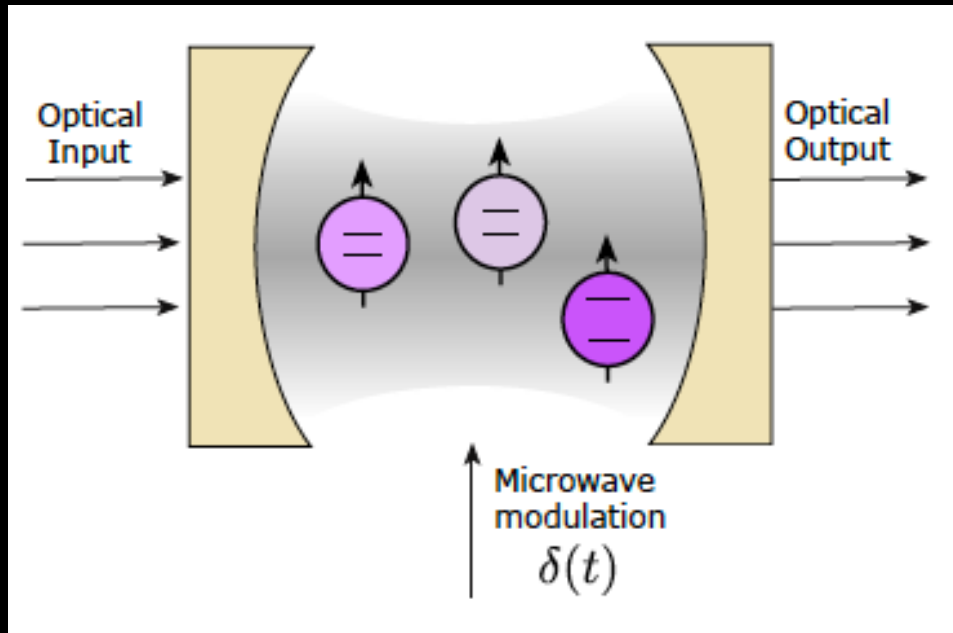
Time-independent Hamiltonian with identical spin resonances.

$$H_0 = \sum_i \frac{\omega_0}{2} \sigma_z^i + \sum_i J [\sigma_+^i \sigma_-^{i+1} + \text{h.c.}]$$

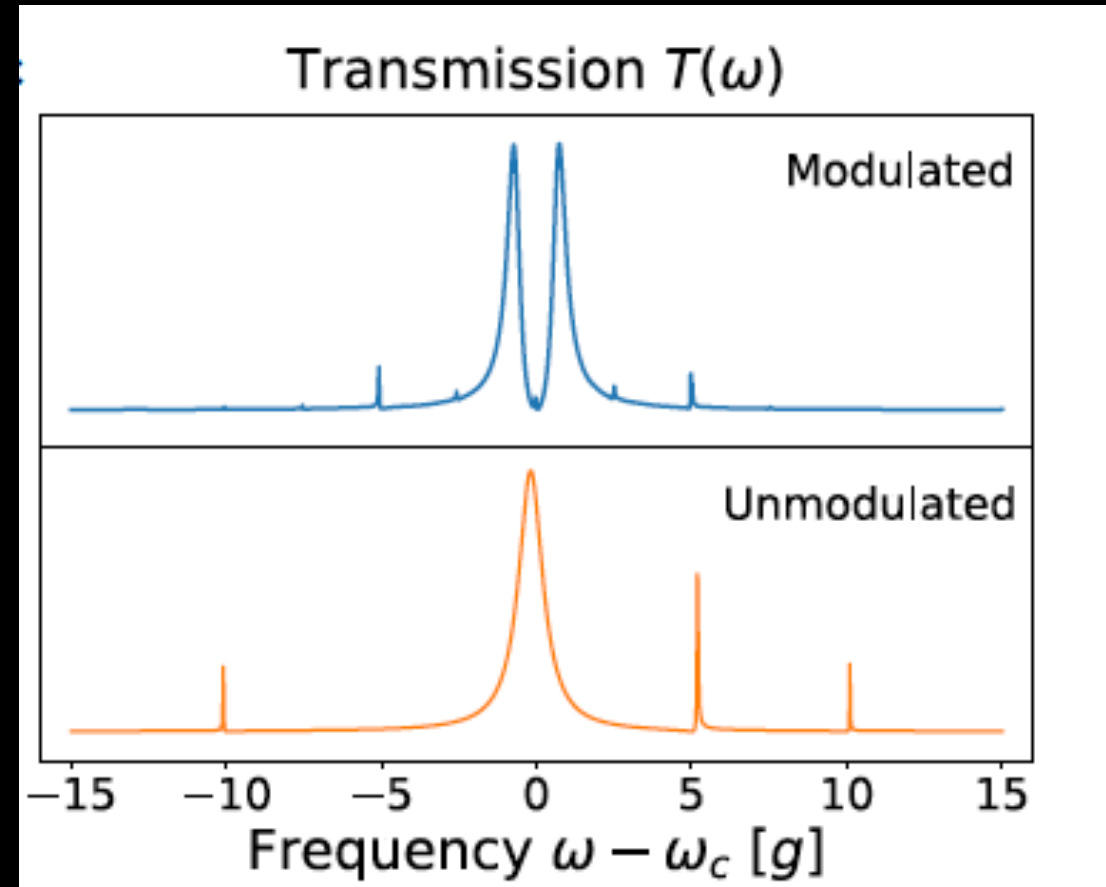
Spectral reconfiguring of VSi in SiC
D. Lukin, A. White, M. Guidry, R. Trivedi et al
[arXiv:2003.12591]

R. Trivedi, S. Sun, in collaboration with
I. Cirac, D. Malz (MPQ)

Inhomogeneous broadening compensation by dynamic modulation

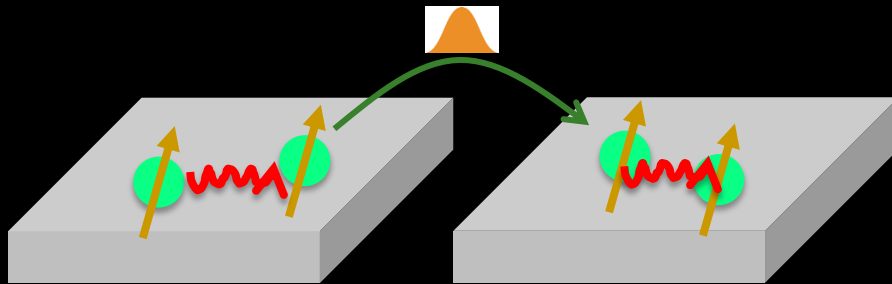


Inhomogeneously broadened emitters under optimized pulsed modulation exhibit signature of collective coupling to cavity mode.



Quantum technologies

Quantum repeaters and networks

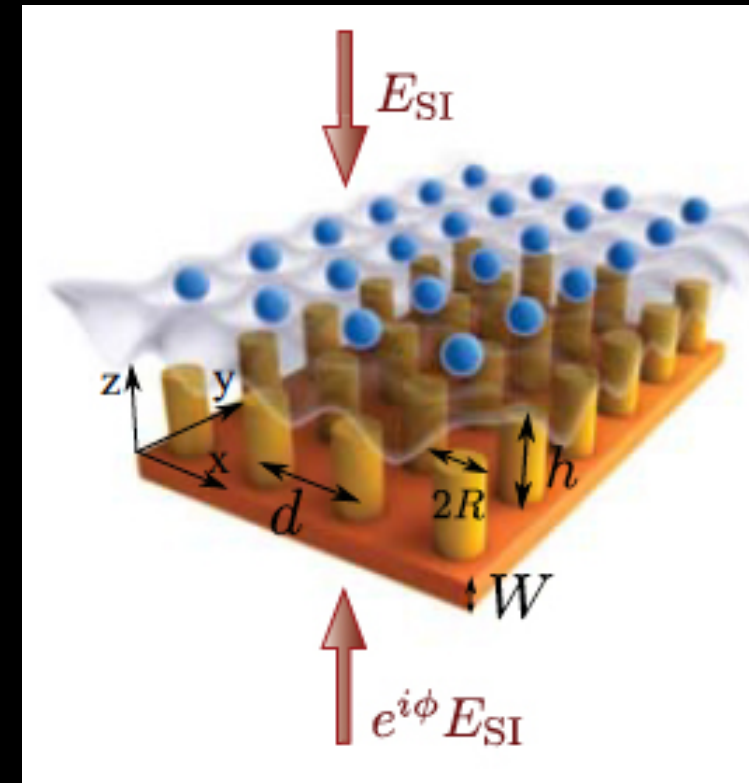


What do we need?

1) Homogeneous, long lived qubits with optical interfaces

2) Efficient optical interconnects

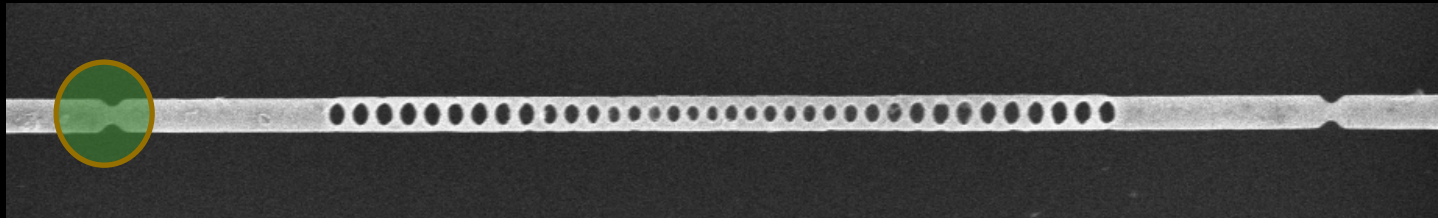
Quantum simulators & computers



Gonzales-Tudela et al., *Nature Photonics* 9, 320-325 (2015).
Douglas et al., *Nature Photonics* 9, 326-331 (2015).

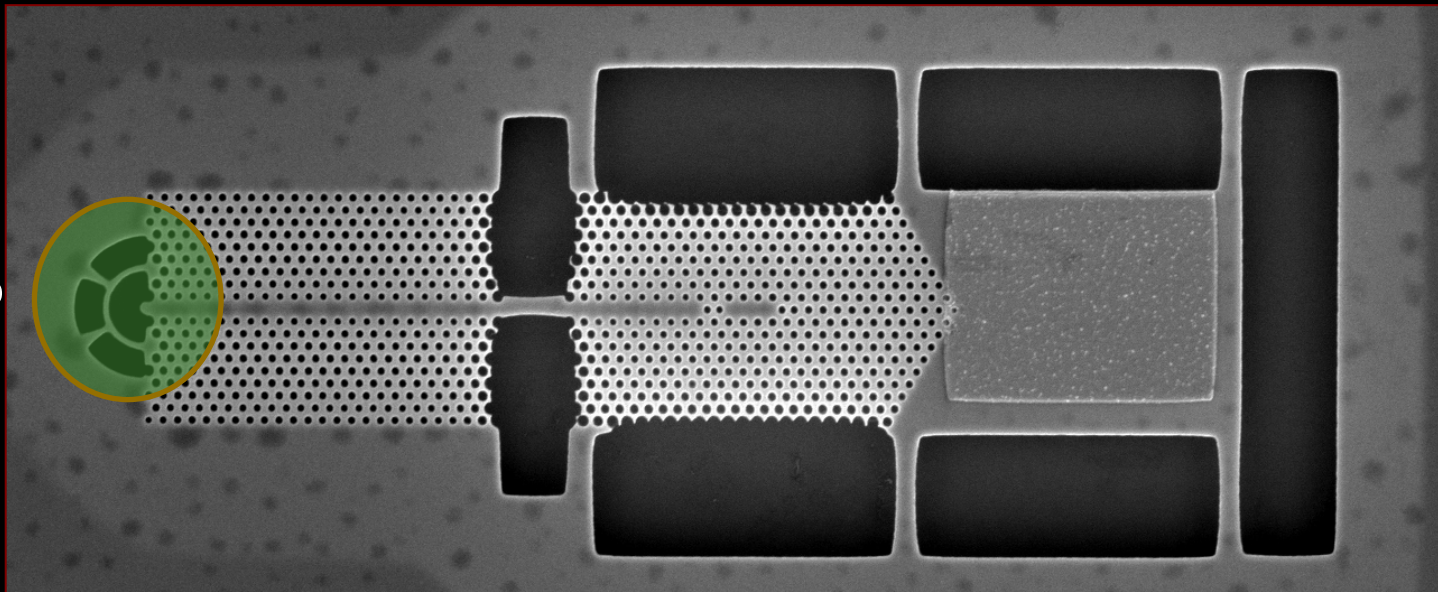
Efficient quantum optical interconnects necessary for system-level integration

1%



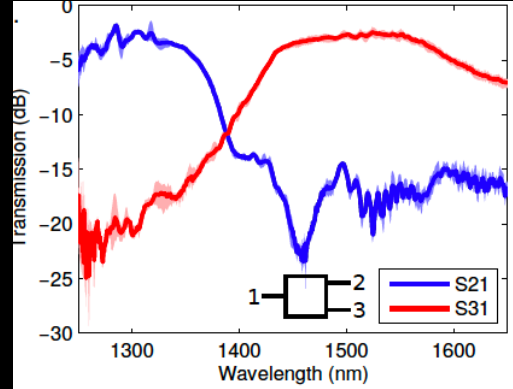
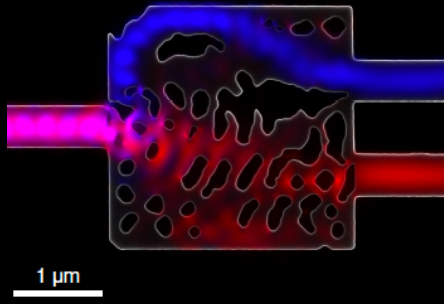
Zhang*, Sun* et al., *Nano Lett.*
18, 1360–1365 (2018)

~5%

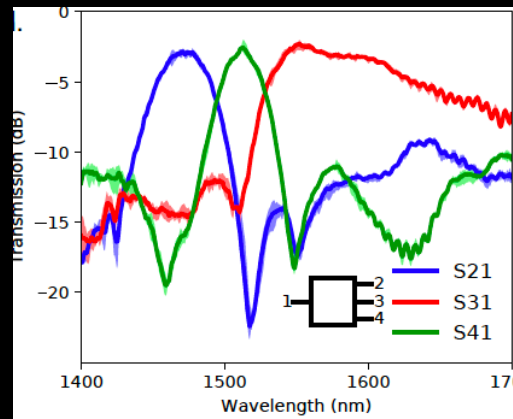
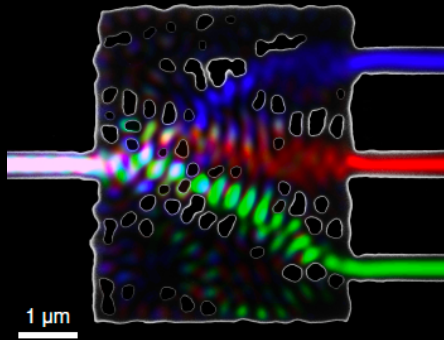


Faraon et al., *Optics Express* 16,
12154 (2008)

Photonics can be efficient, robust, and insensitive to errors



A. Piggott et al,
Nature Photonics (2015)



L. Su et al, *ACS Photonics*, 5 (2),
pp 301–305 (2018)

Logan Su et al, *Appl. Phys. Rev.* 7, 011407 (2020)

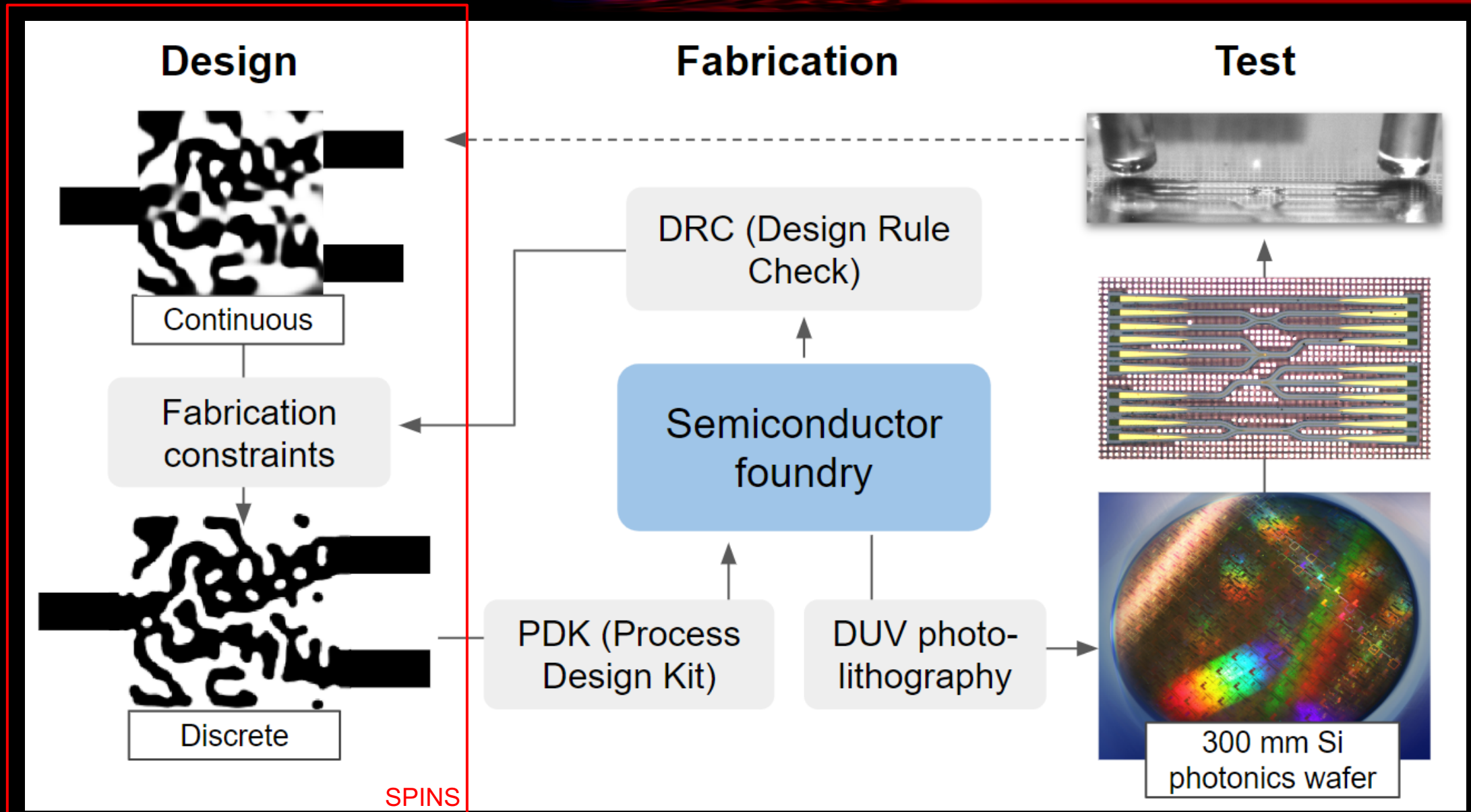
Stanford Photonics INverse design Software (SPINS)

Vuckovic Group - Stanford OTL Docket Number: S18-012

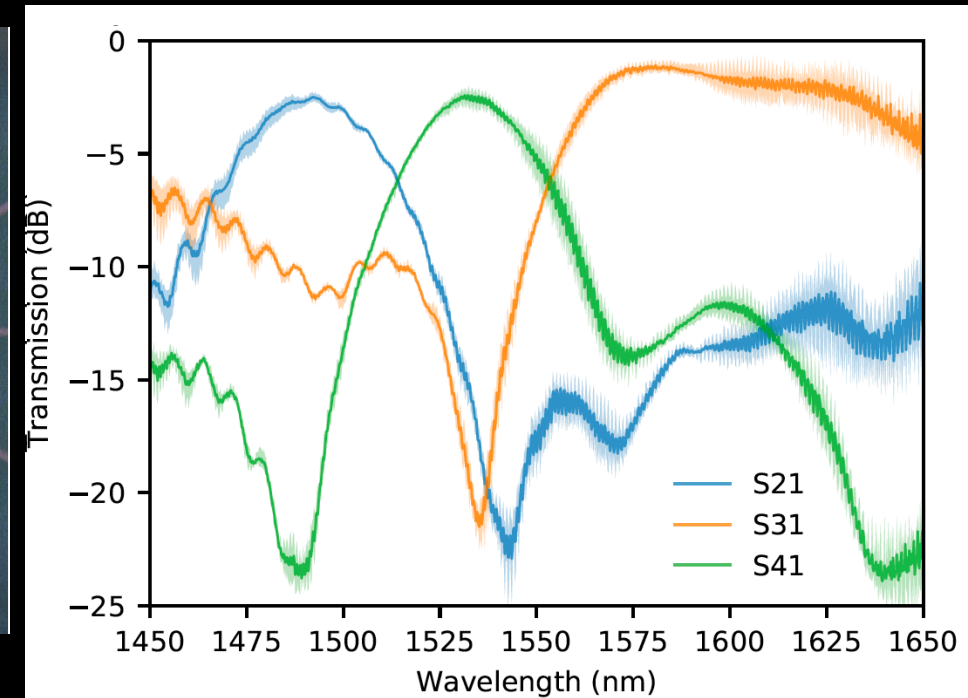
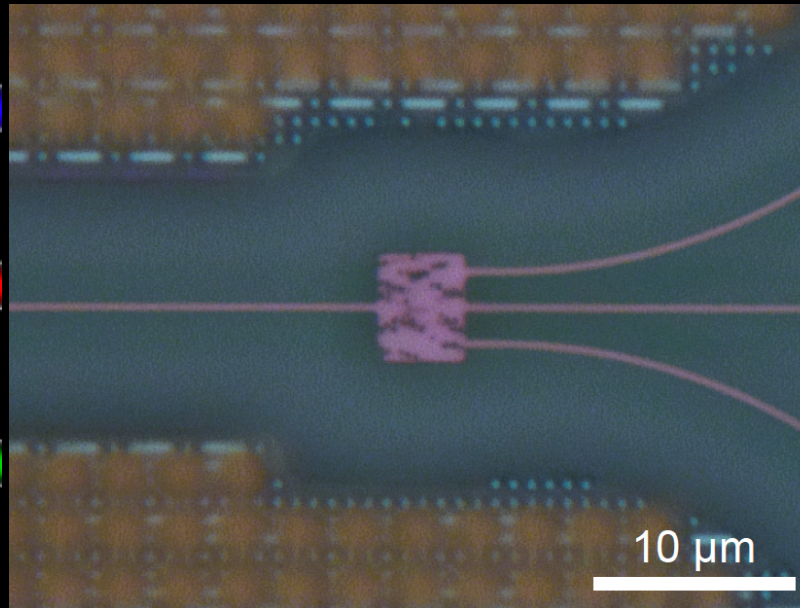
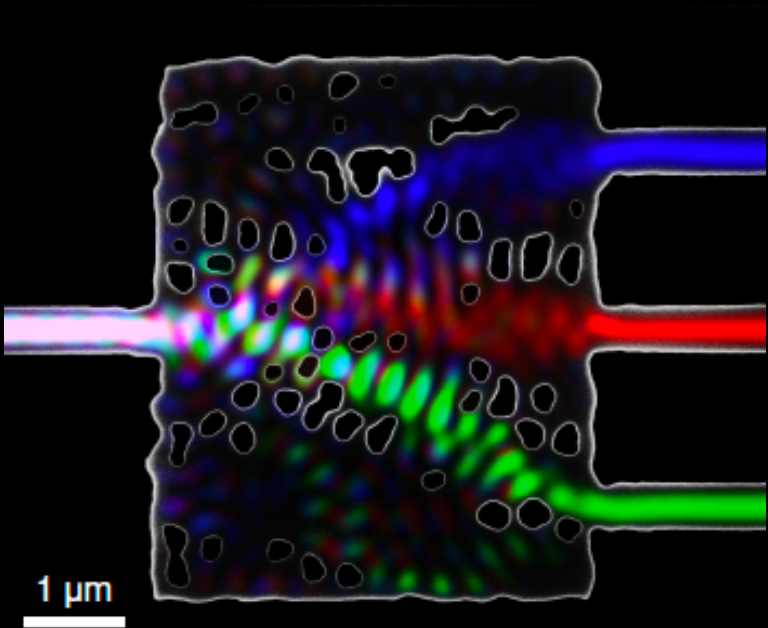
SPINS-B (open source, 3D) on Github

<http://github.com/stanfordnqp/spins-b>

Foundry fabricated inverse designed photonics



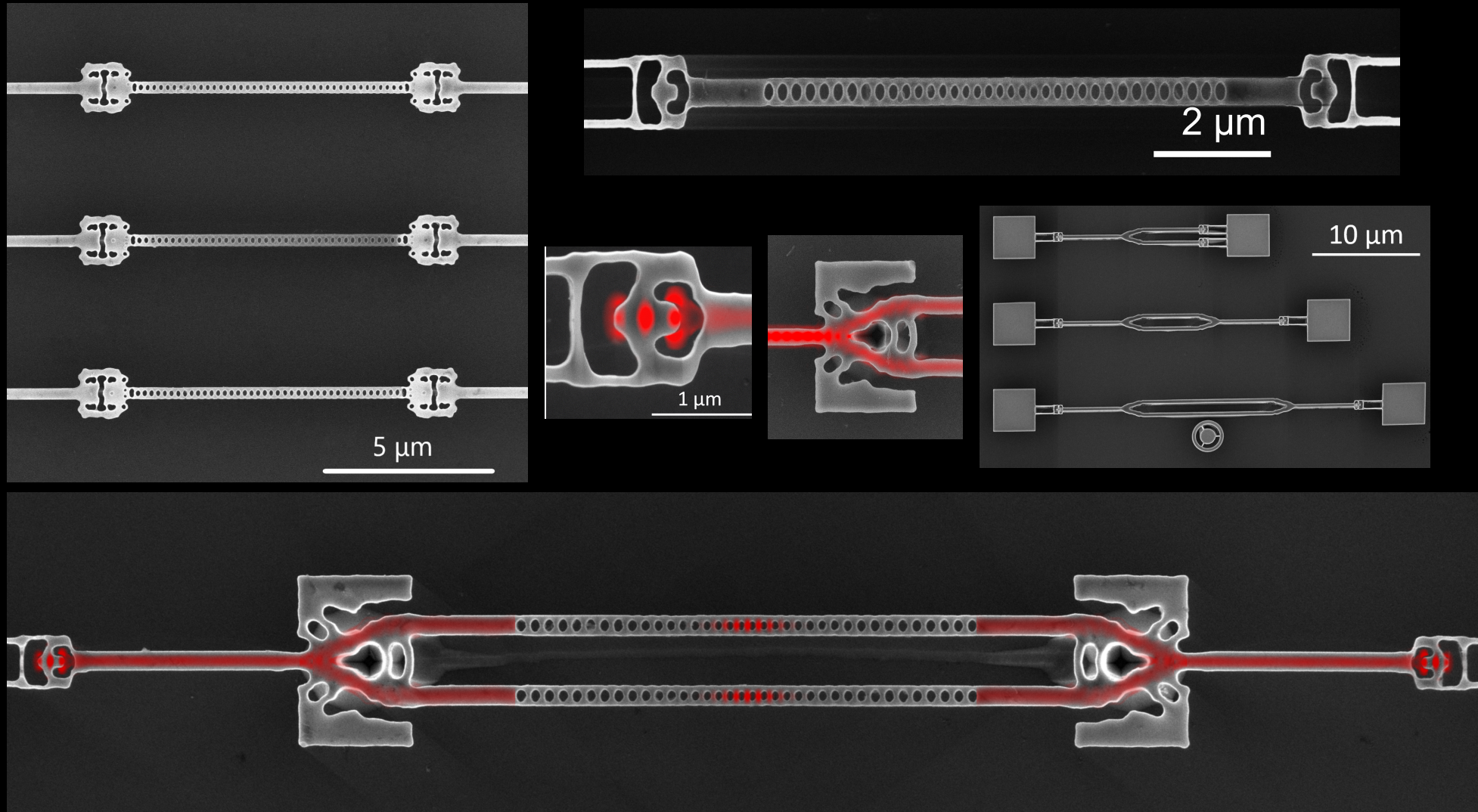
Foundry fabricated inverse designed photonics



L. Su et al, *ACS Photonics*, 5
(2), pp 301–305 (2018)

Collaboration with John Bowers, UCSB
Piggott, E. Ma, L. Su et al, *ACS Photonics*
<https://doi.org/10.1021/acsp Photonics.9b01540> (2020)

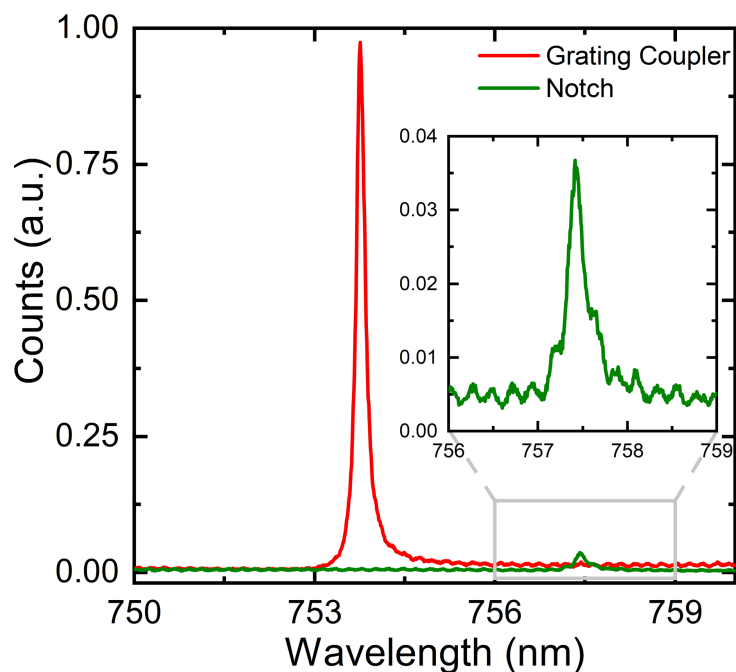
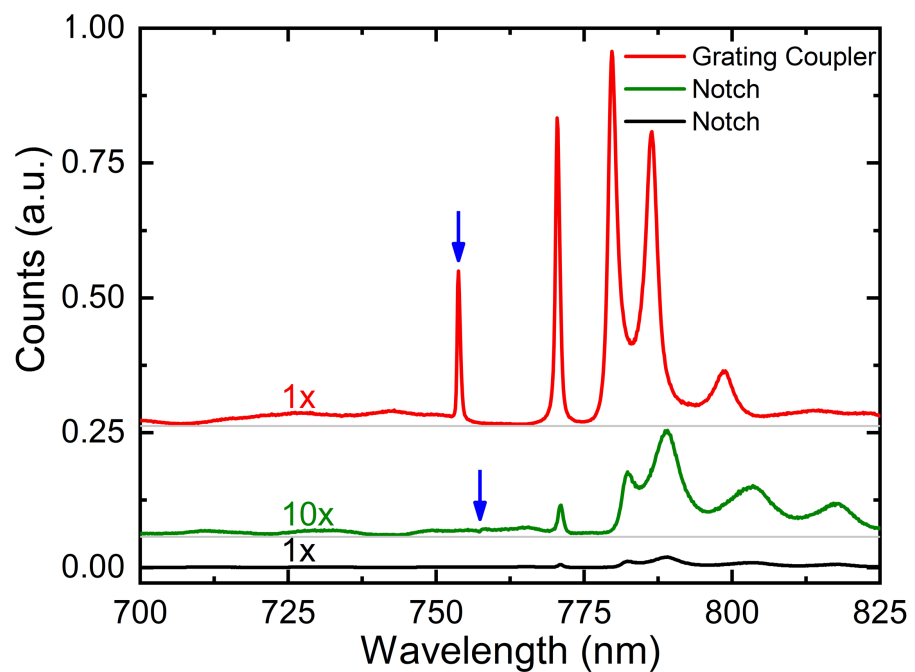
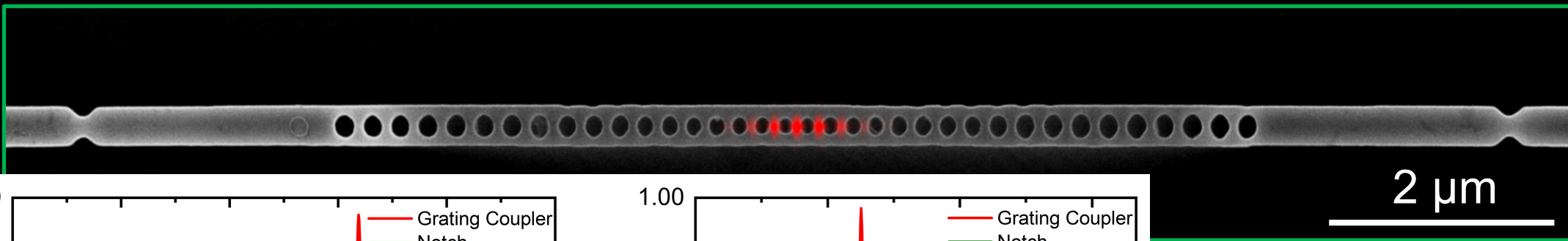
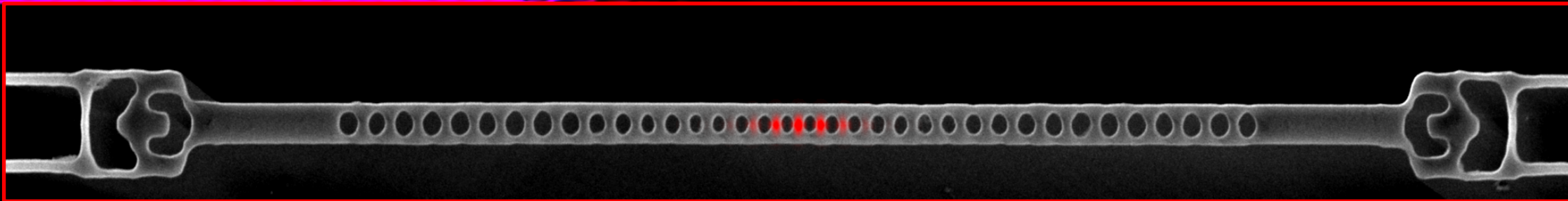
Optimized diamond quantum photonics



Fabrication method developed by Constantin Dory, Daniil Lukin
(inspired by work from Paul Barclay, Calgary; Dirk Englund, MIT)

C. Dory, et al., *Nature Comm.* 10,
3309 (2019)

Optimized coupler-cavity integration

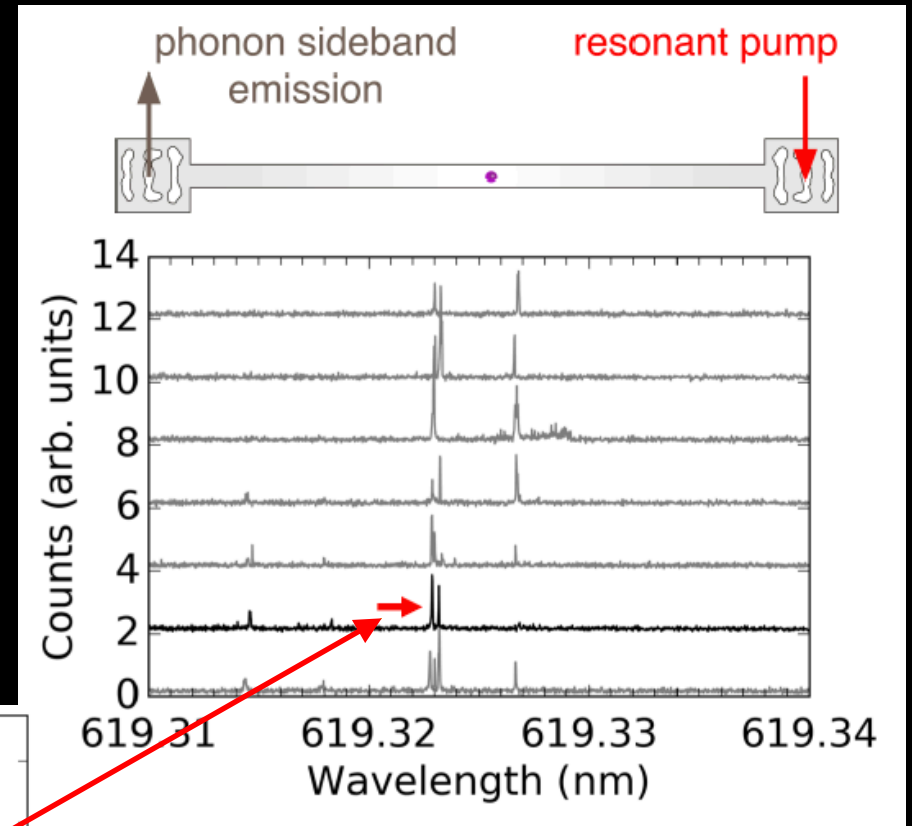
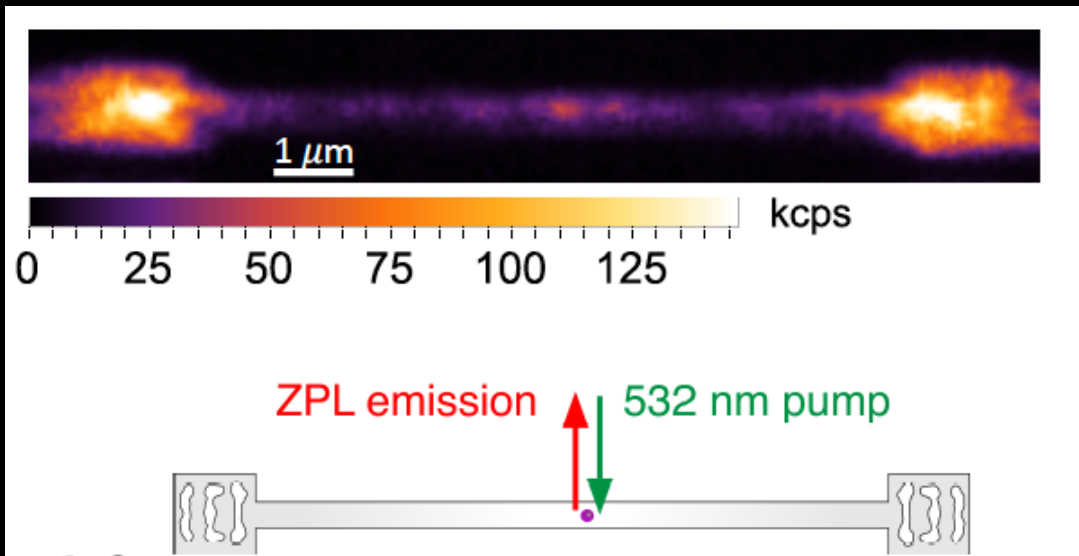


$Q \sim 10-15 \cdot 10^3$

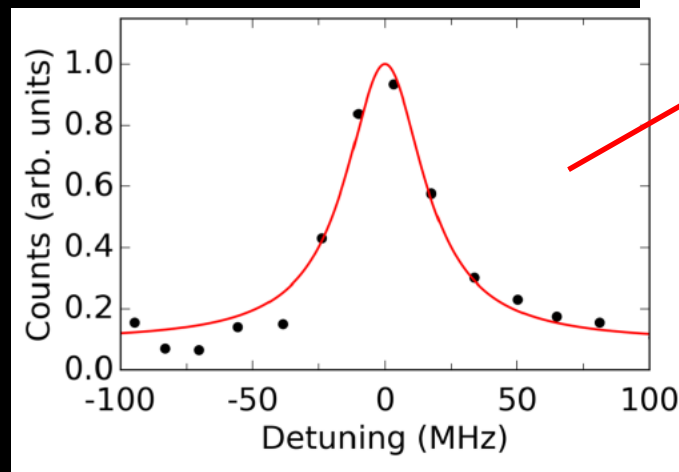
- ~500-fold enhancement in counts, reduction in experimental time!
- Easier to scale to multiple nodes

C. Dory, et al., *Nature Comm.* 10, 3309 (2019)

SnV coupling to diamond photonics



- Combined SIIG and diamond fab
- ~ 30 MHz linewidth of SnV- in diamond photonic structures, on par with best bulk PLE measurements



A. Rugar, C. Dory, S. Aghaeimeibodi et al
[arXiv:2005.10385]

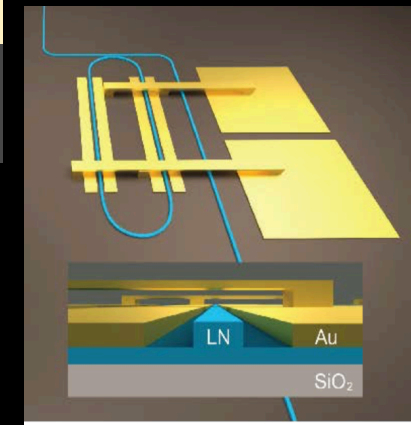
Silicon Carbide - ideal photonics material

- Strong optical nonlinearity
- Piezoelectric
- Excellent thermal conductivity
- Large bandgap
- Silicon compatible
- Available on wafer scale
- Host high quality quantum emitters – color centers
=> quantum technologies

1960's: Silicon (Si) wafers commercialized.
2000's: Silicon-on-Insulator (SOI) commercialized.
→ Silicon photonics enters golden age.

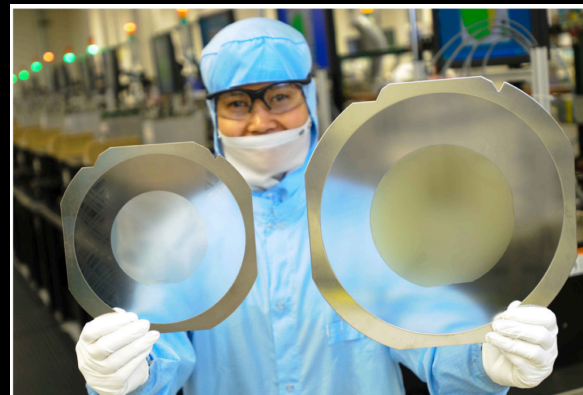


1990's: Lithium Niobate (LiNbO₃) wafers commercialized.
2010's: LiNbO₃-on-Insulator is commercialized.
→ LiNbO₃ photonics



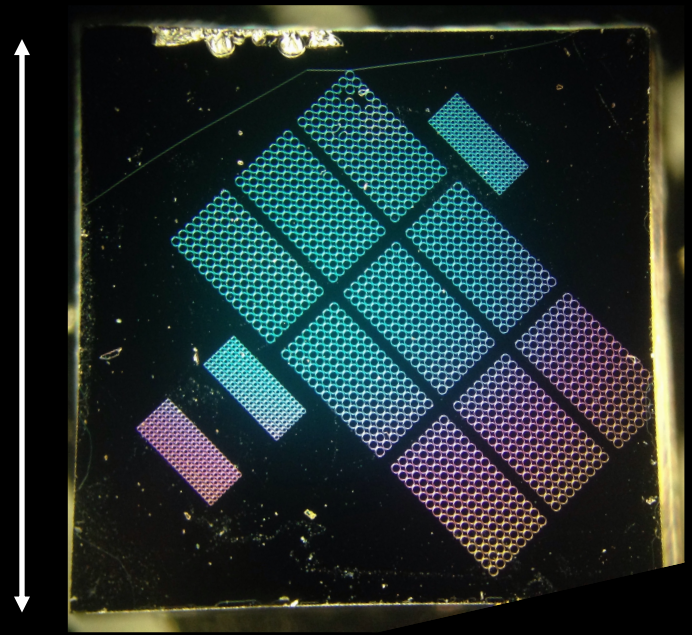
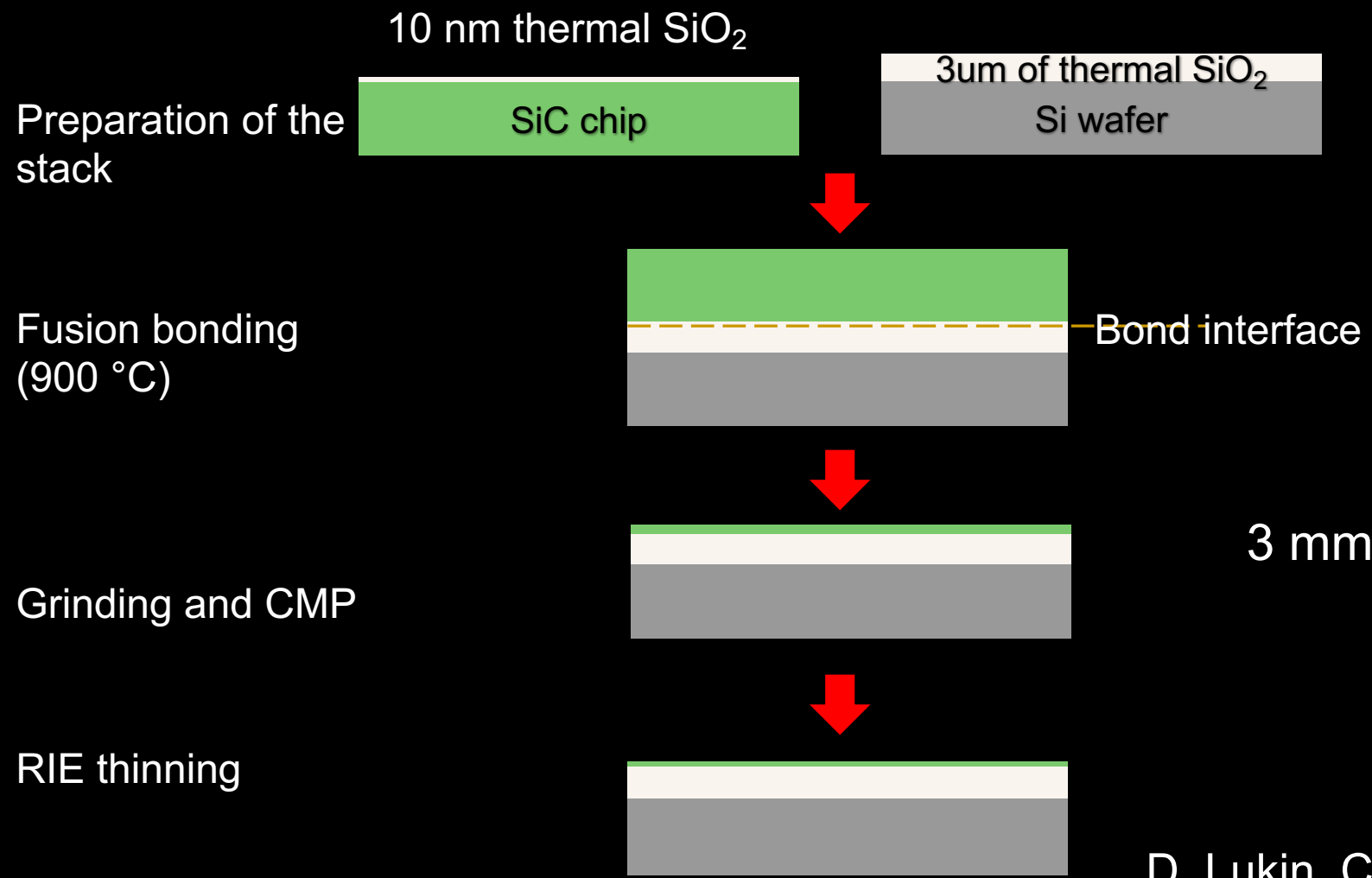
C. Wang, Opt. Express 26, 2018

1990's: SiC wafers commercialized...
2019: SiC-on-insulator?

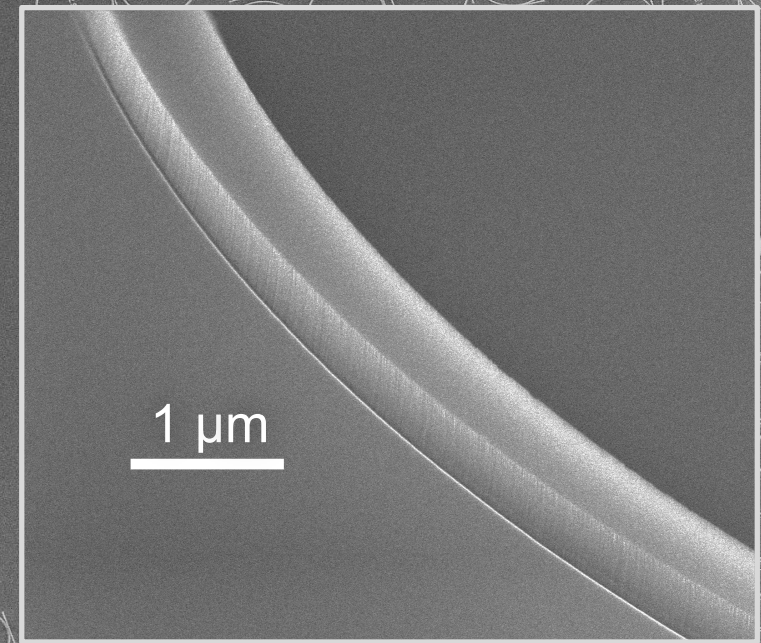
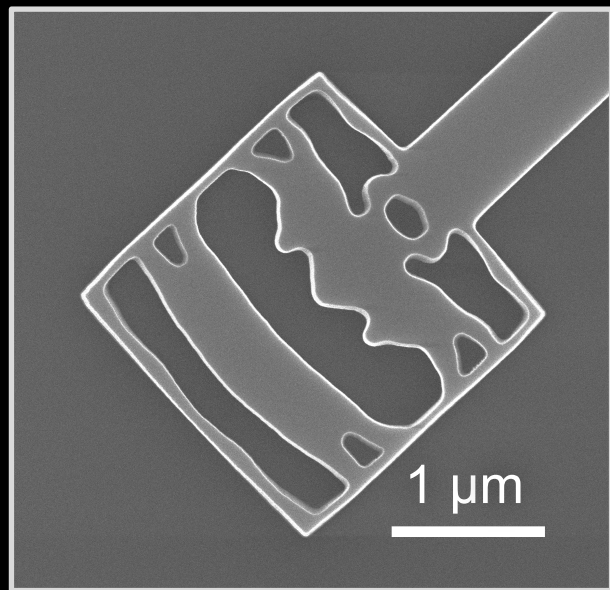
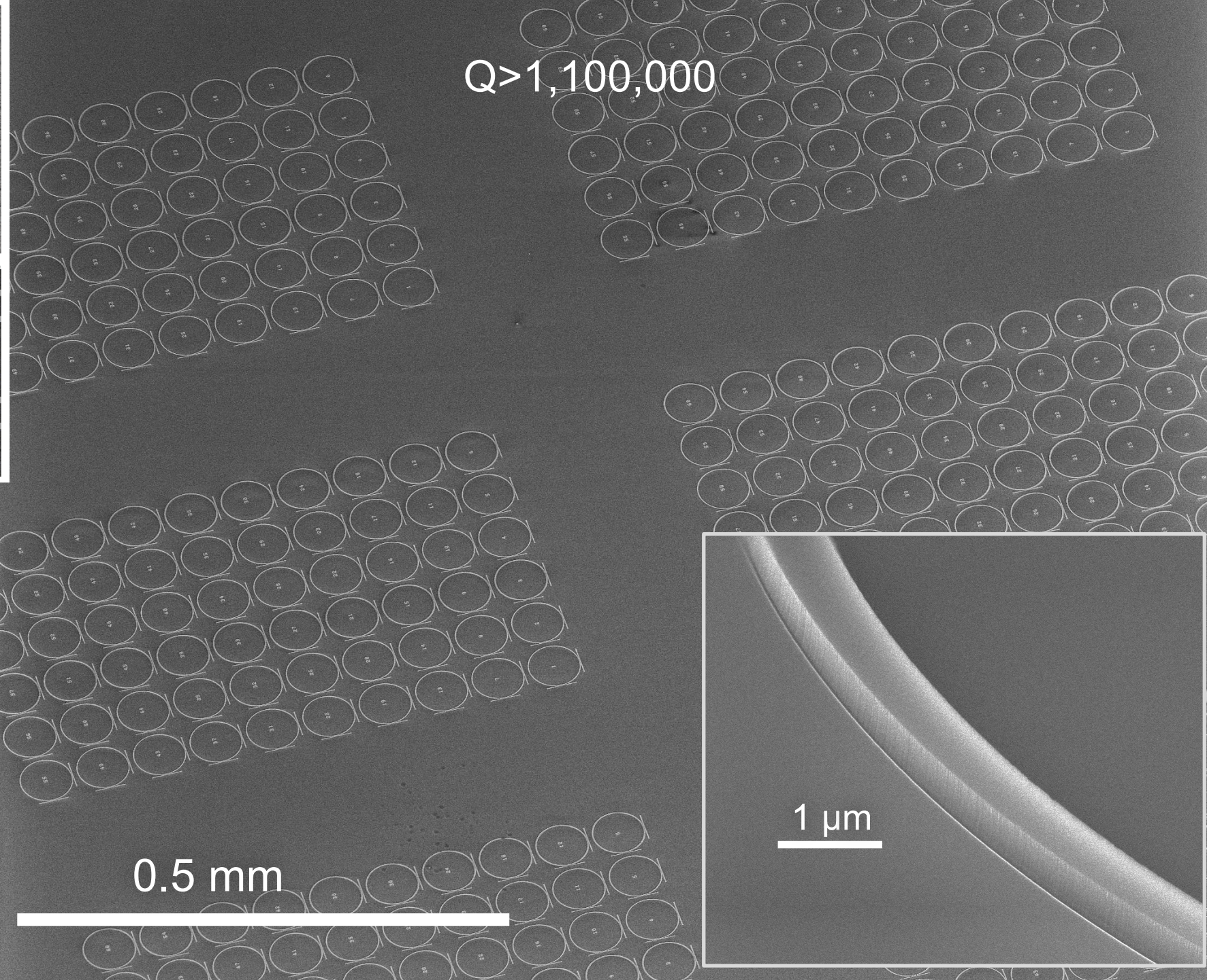
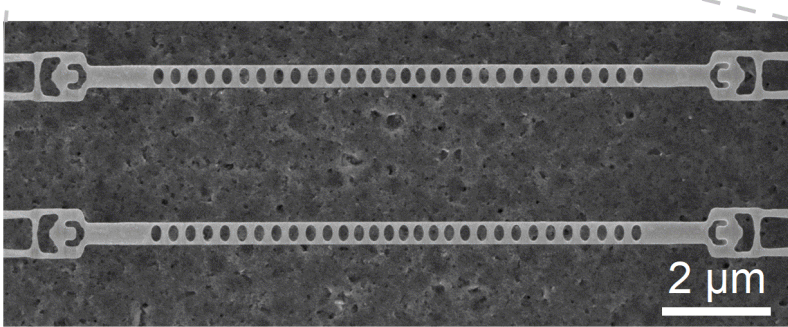
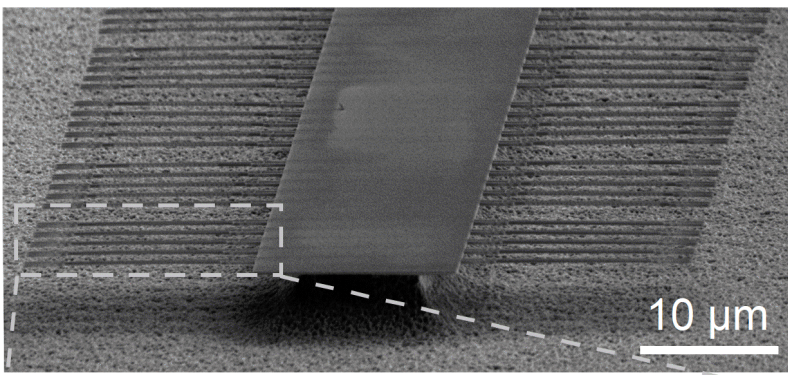


100 mm and 150 mm 4H-SiC wafers (CREE)

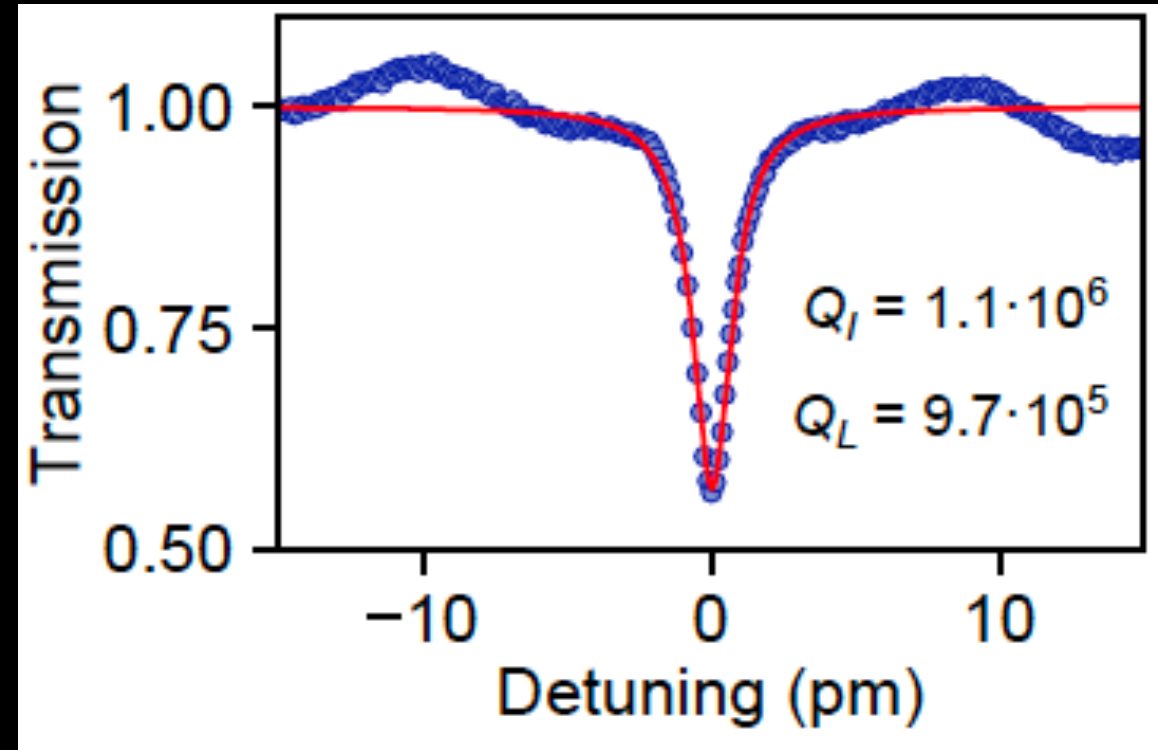
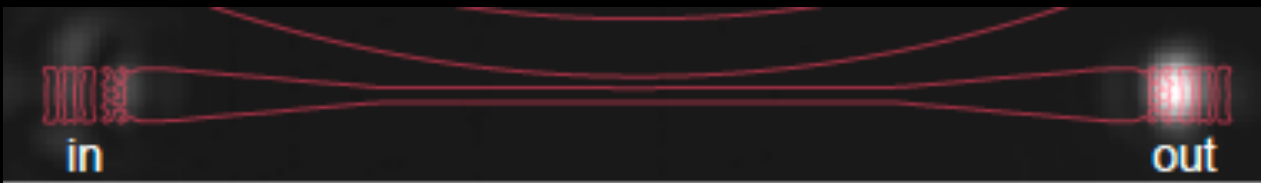
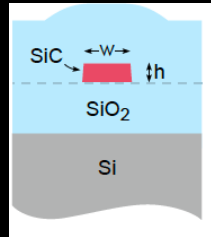
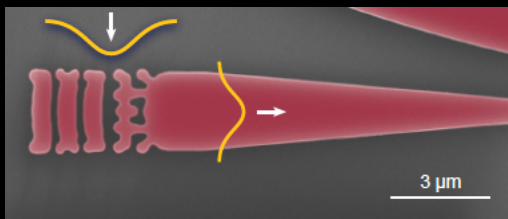
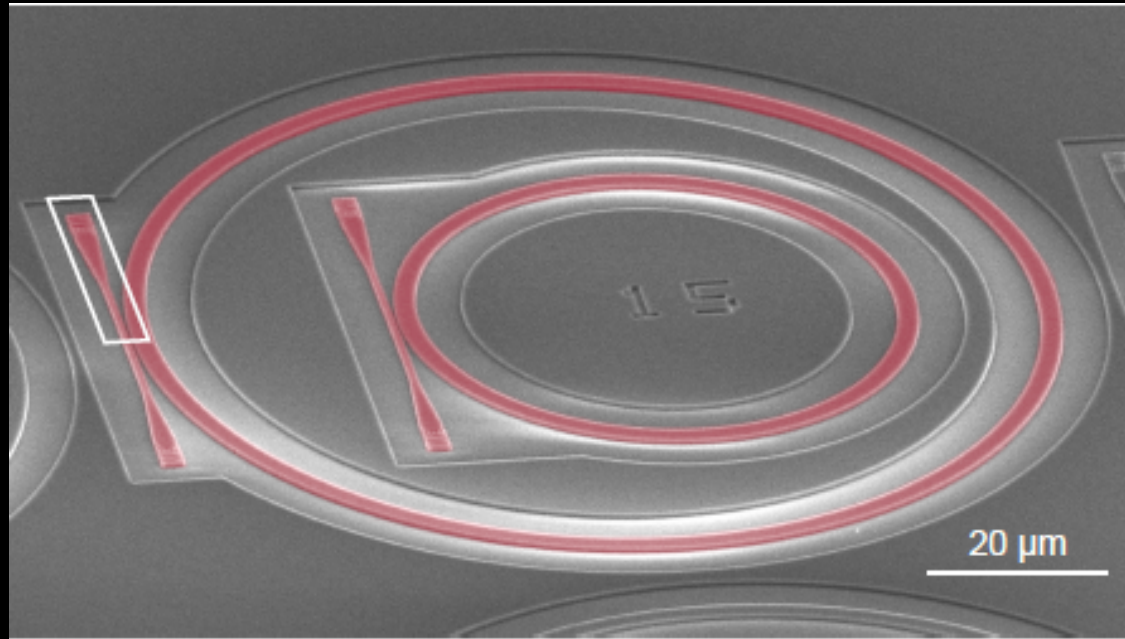
SiCOI (SiC on Insulator)



D. Lukin, C. Dory, M. Guidry et al,
Nature Photonics vol.14, pp. 330–334 (2020)



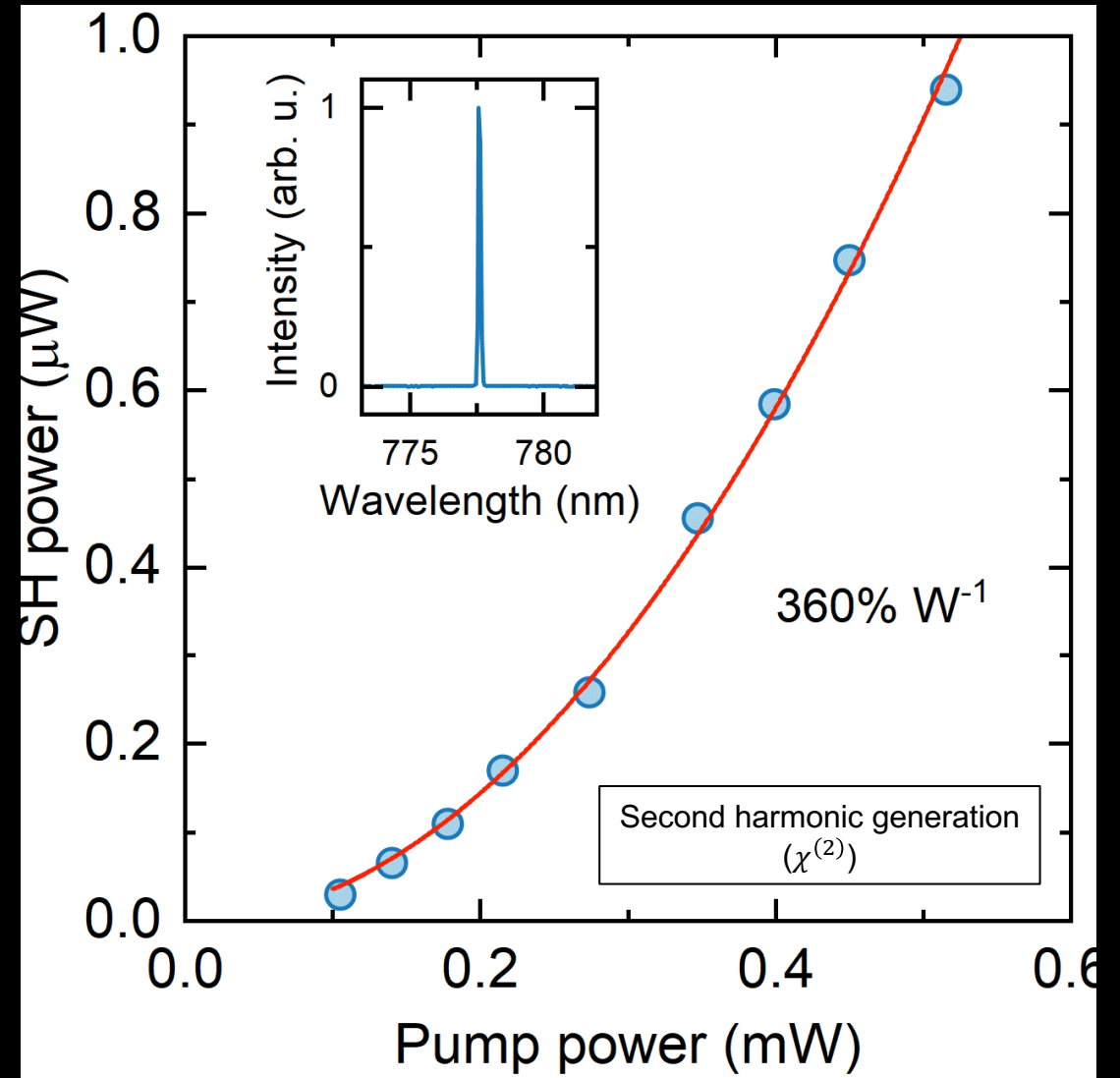
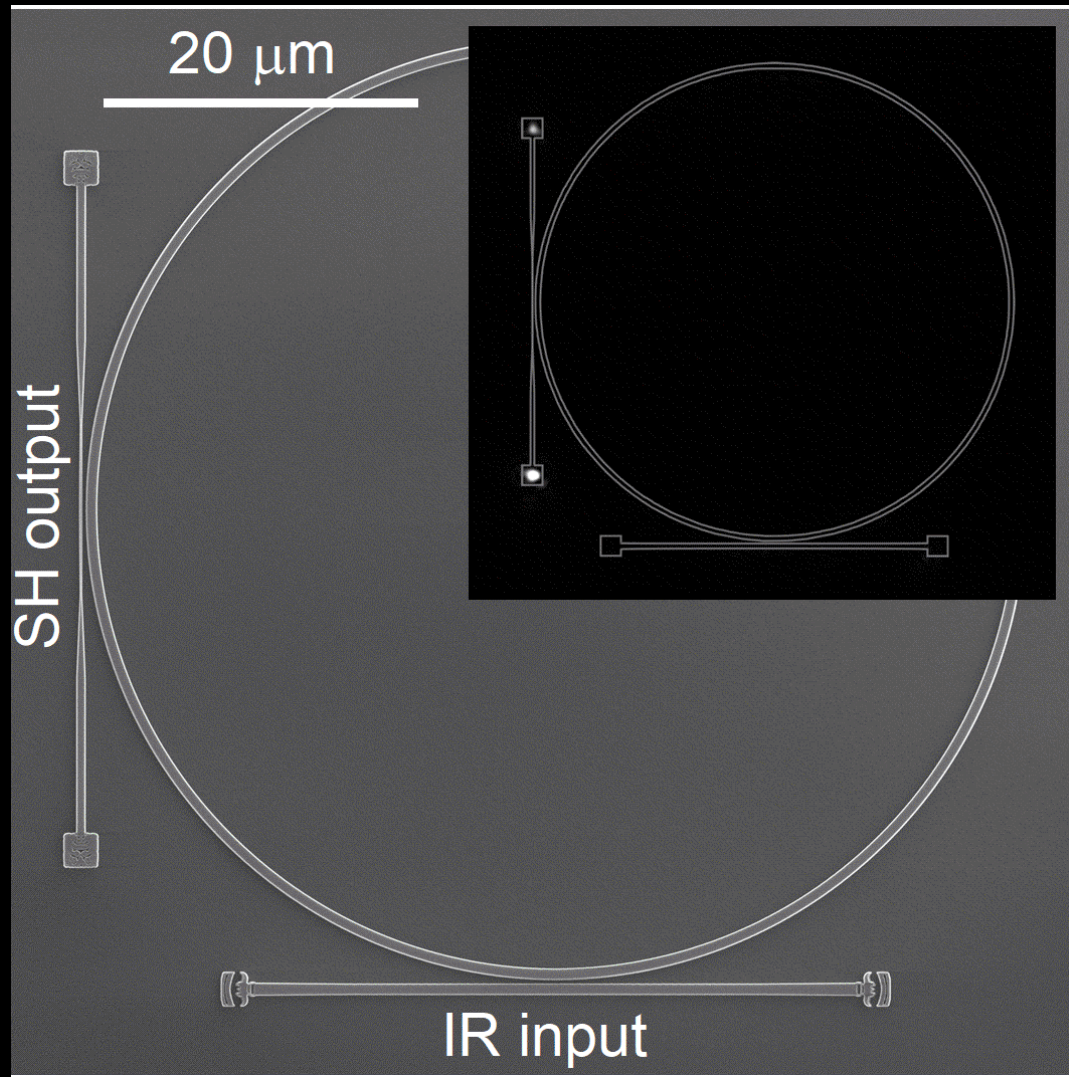
SiCOI photonics



D. Lukin, C. Dory, M. Guidry et al,
Nature Photonics vol.14, pp. 330–334 (2020)

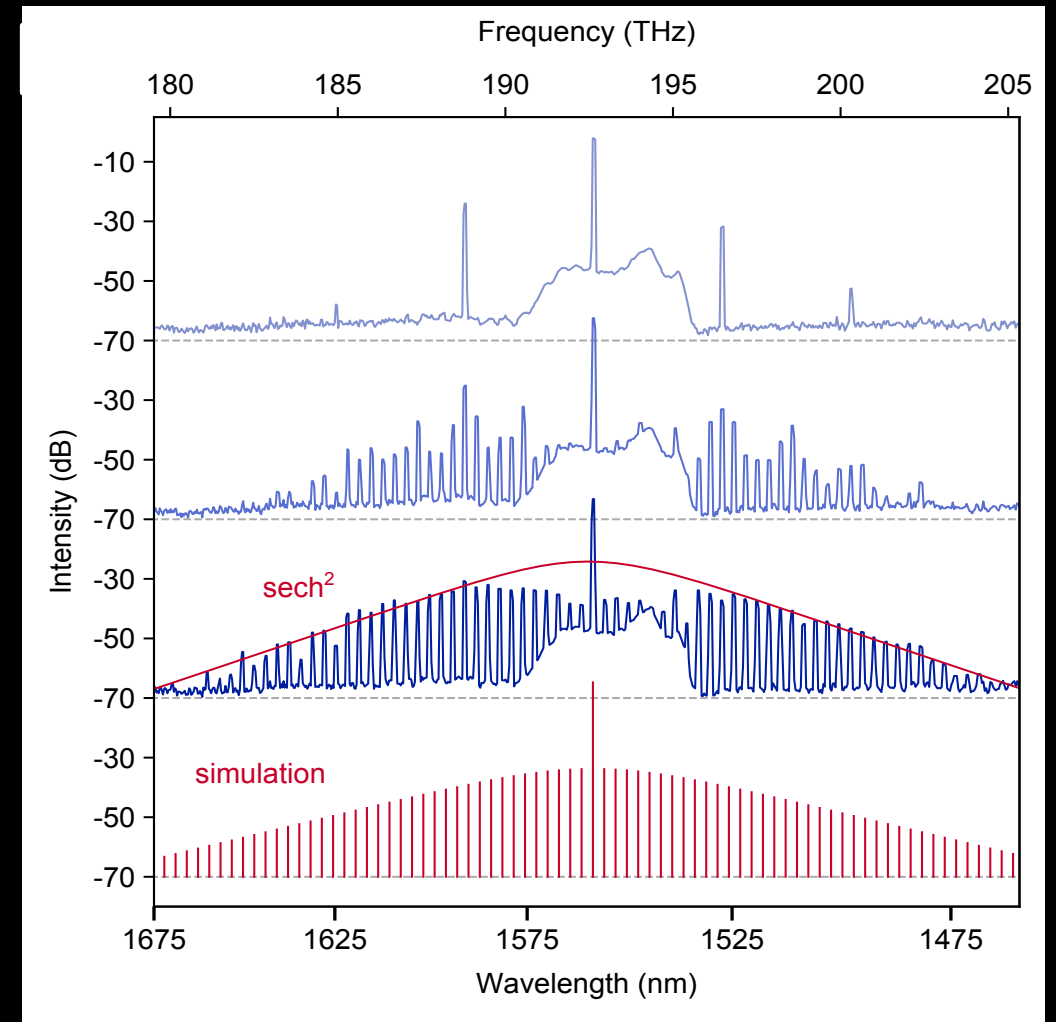
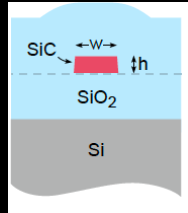
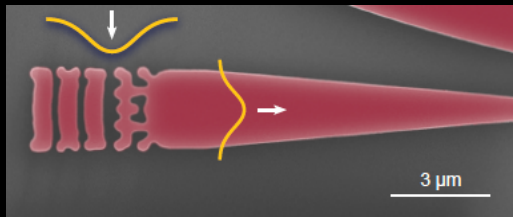
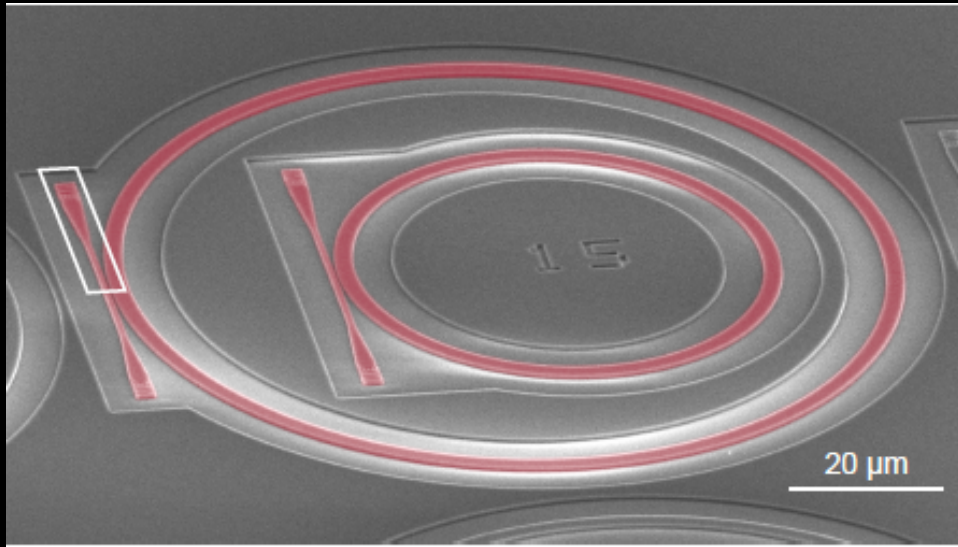
M. Guidry, K. Yang, D. Lukin et al [arXiv:2004.13958]

SiCOI nonlinear photonics



D. Lukin, C. Dory, M. Guidry et al,
Nature Photonics vol.14, pp. 330–334 (2020)

Nonlinear photonics: optical parametric oscillation (OPO)

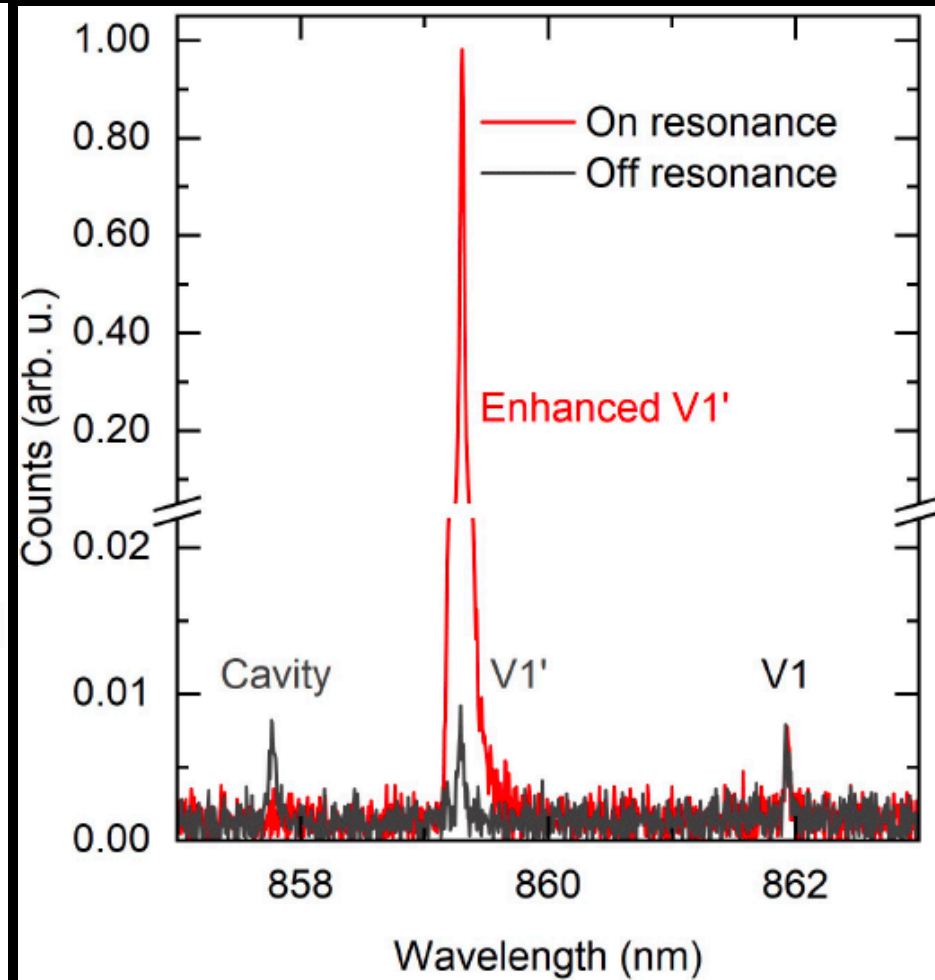
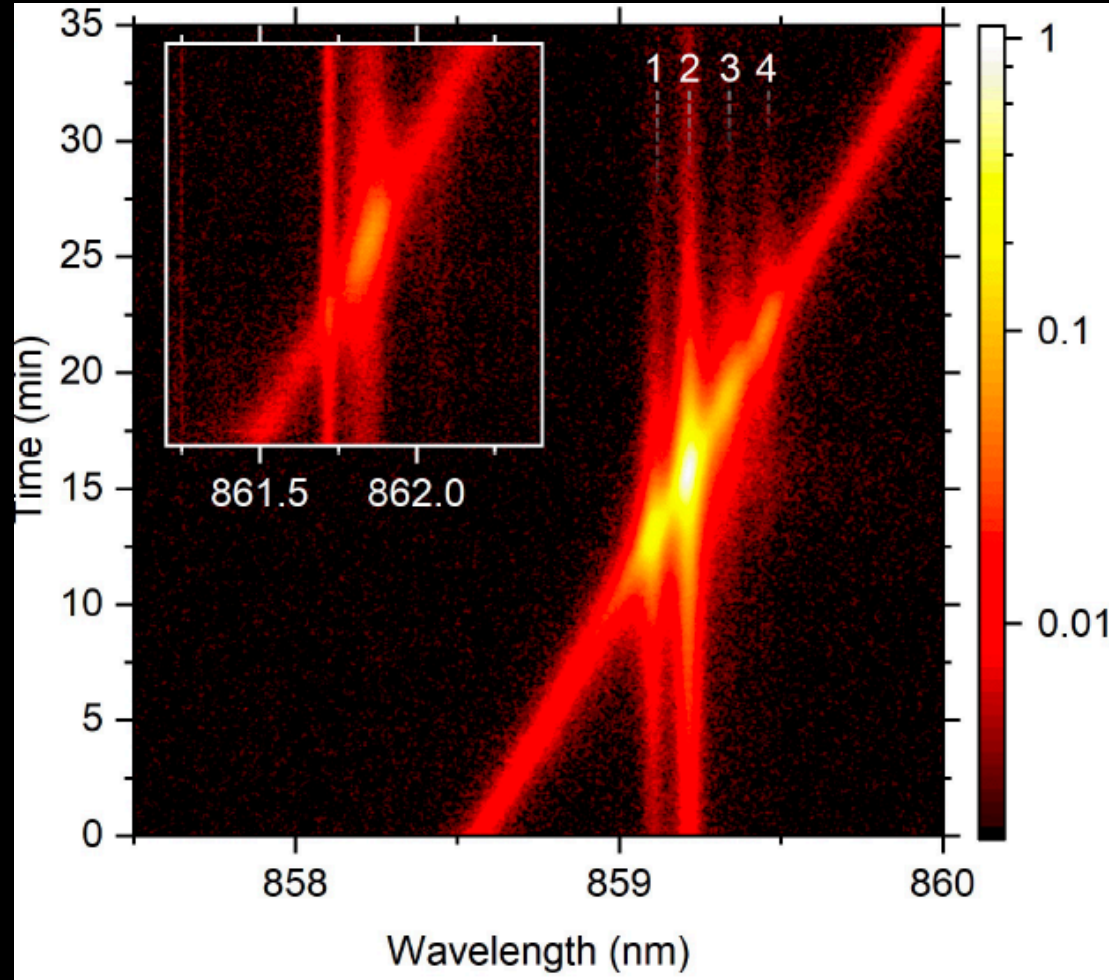
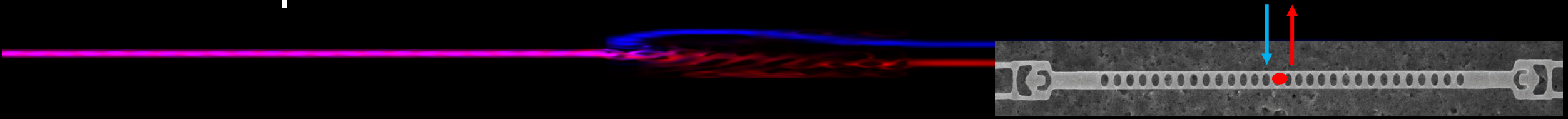


M. Guidry, K. Yang, D. Lukin et al [arXiv:2004.13958]

Four-wave-mixing
($\chi^{(3)}$)

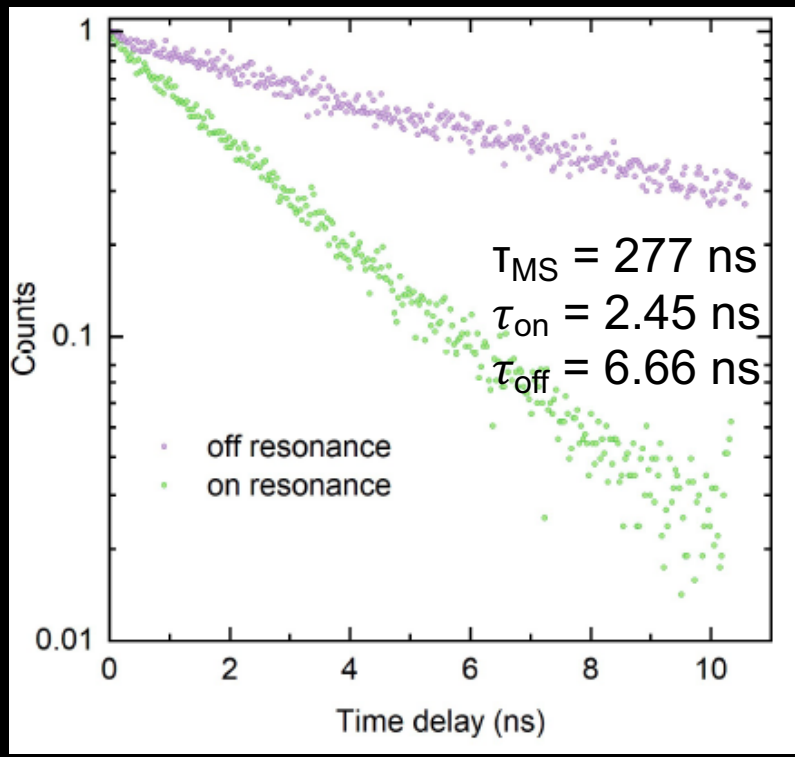
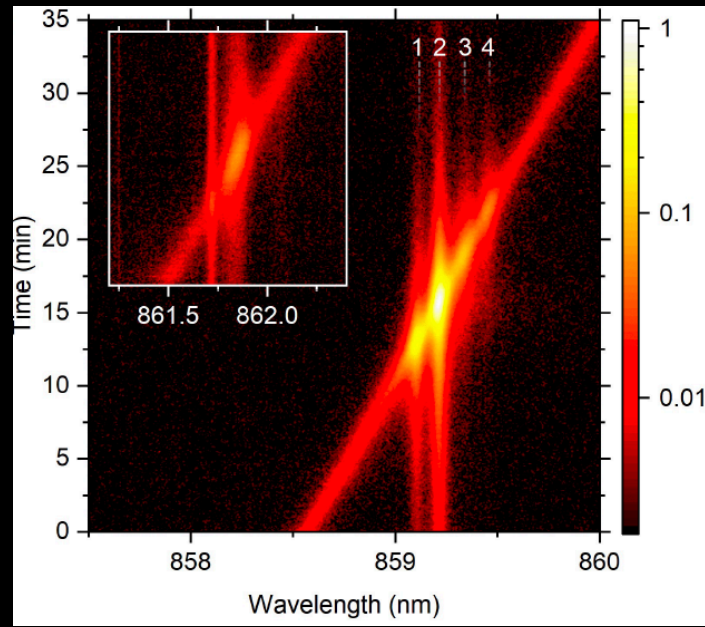
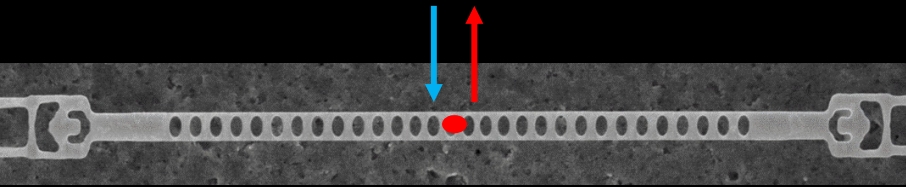
8mW threshold
for OPO

Quantum photonics: interaction with color centers



~100-fold
enhancement
on cavity
resonance

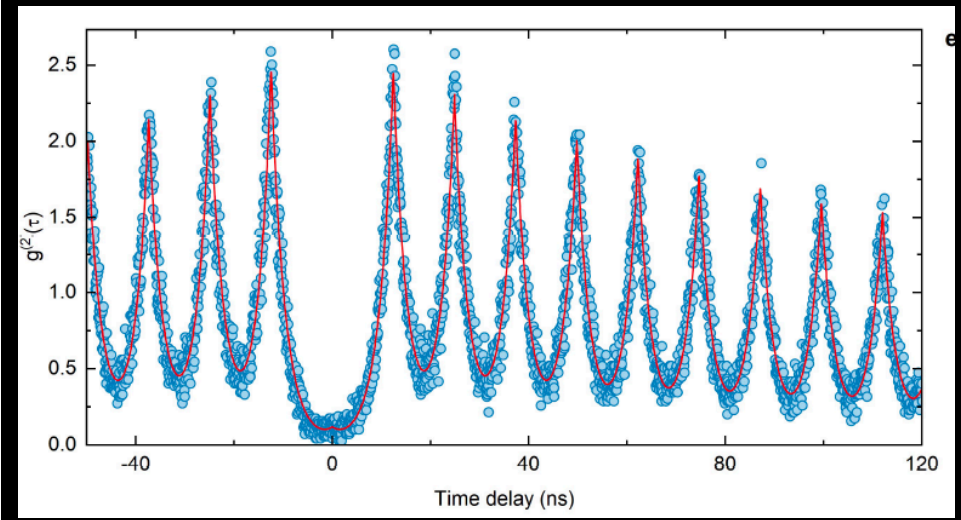
Purcell enhancement



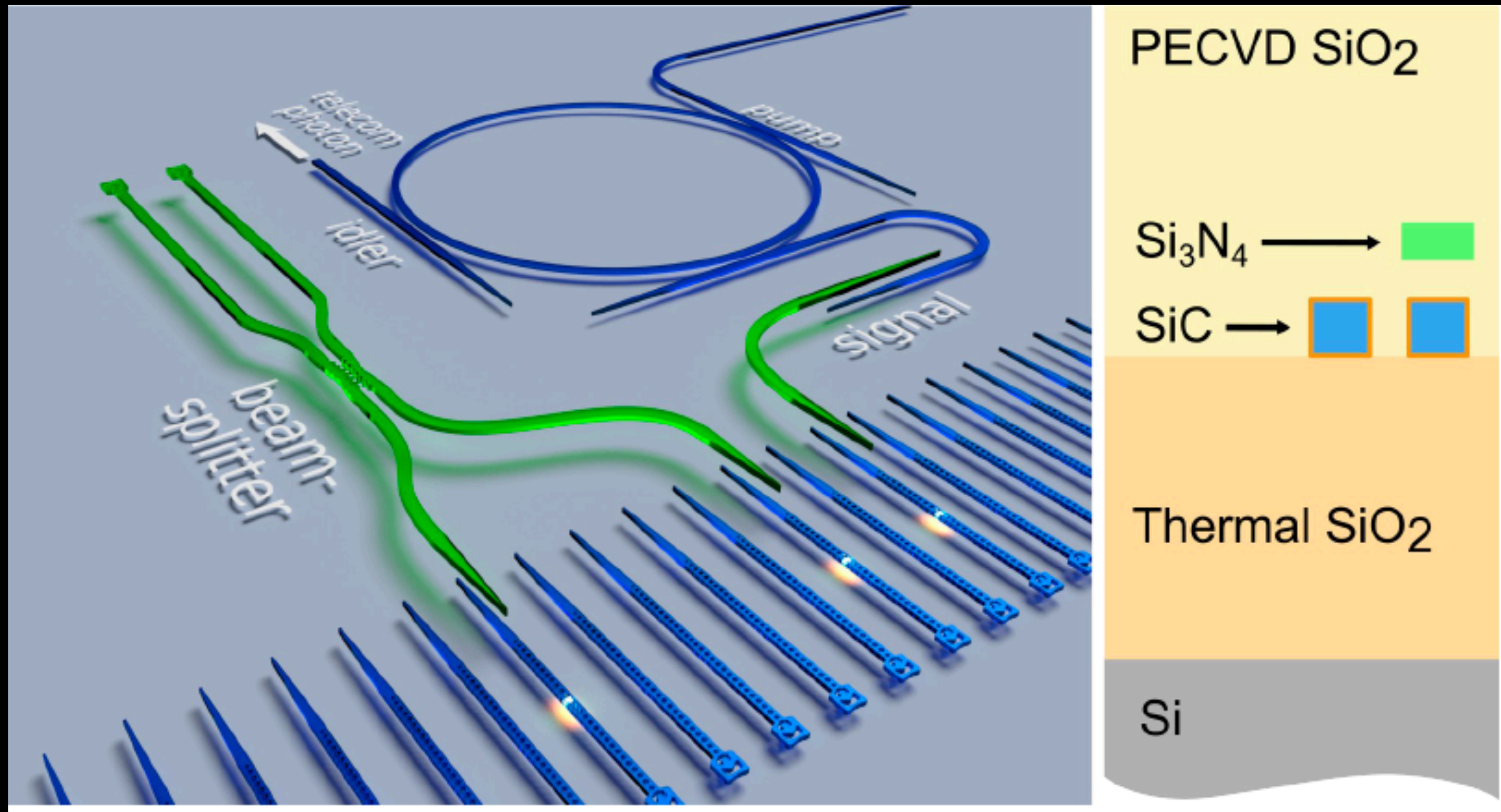
Purcell Enhancement Lower Bound: $F = \frac{\tau_{off} - 1}{\tau_{on} \xi}$

$\xi = 0.19$ Debye-Waller Factor (upper limit)

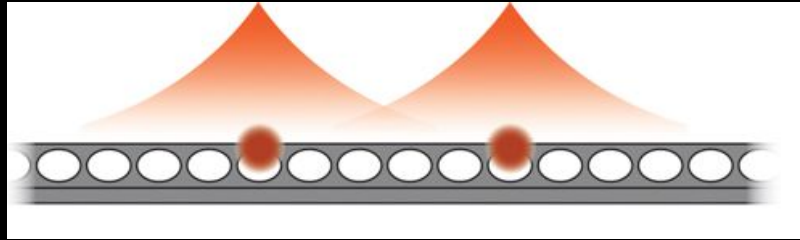
$F \gg 9$



Outlook – SiCOI chip-scale quantum networks

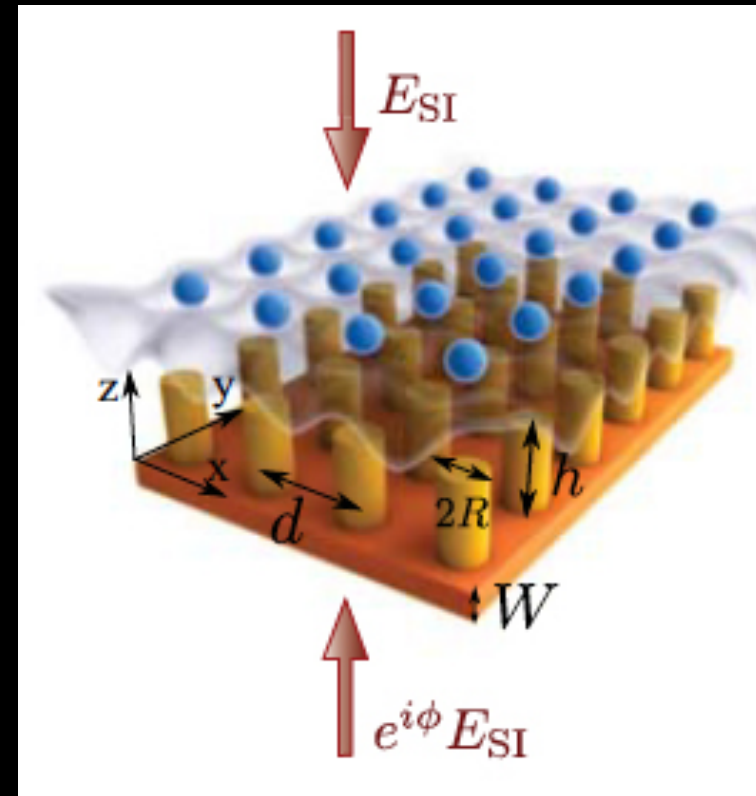


Outlook: solid-state quantum simulators



$$H_I \approx \frac{\hbar \bar{g}_c^2}{\Delta_c} \sum_{j,l} \sigma_{eg}^j \sigma_{ge}^l f(z_j, z_l)$$

We can specify an interaction Hamiltonian by inverse engineering the photonic environment!

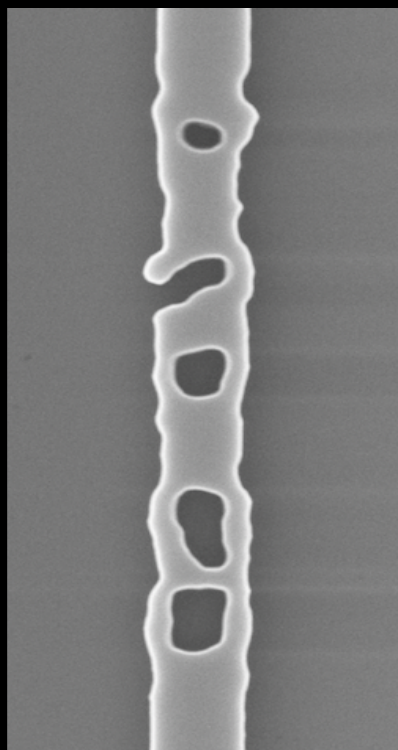
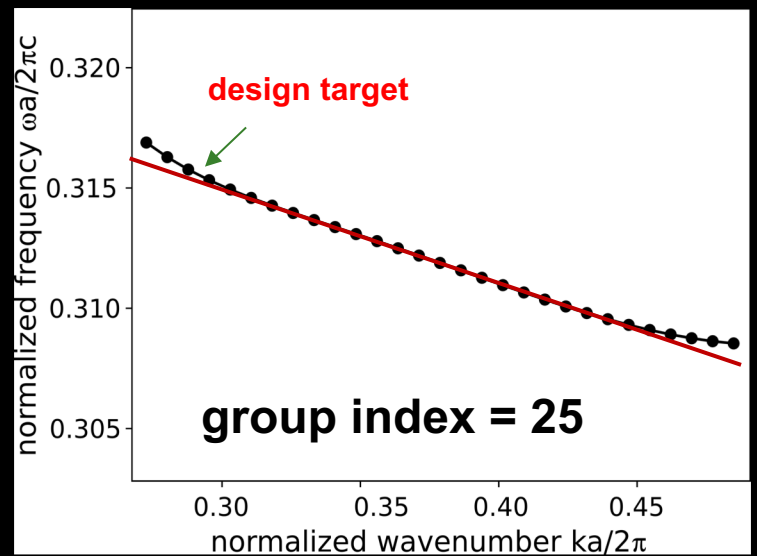


González-Tudela et al., *Nature Photonics* 9, 320–325 (2015).

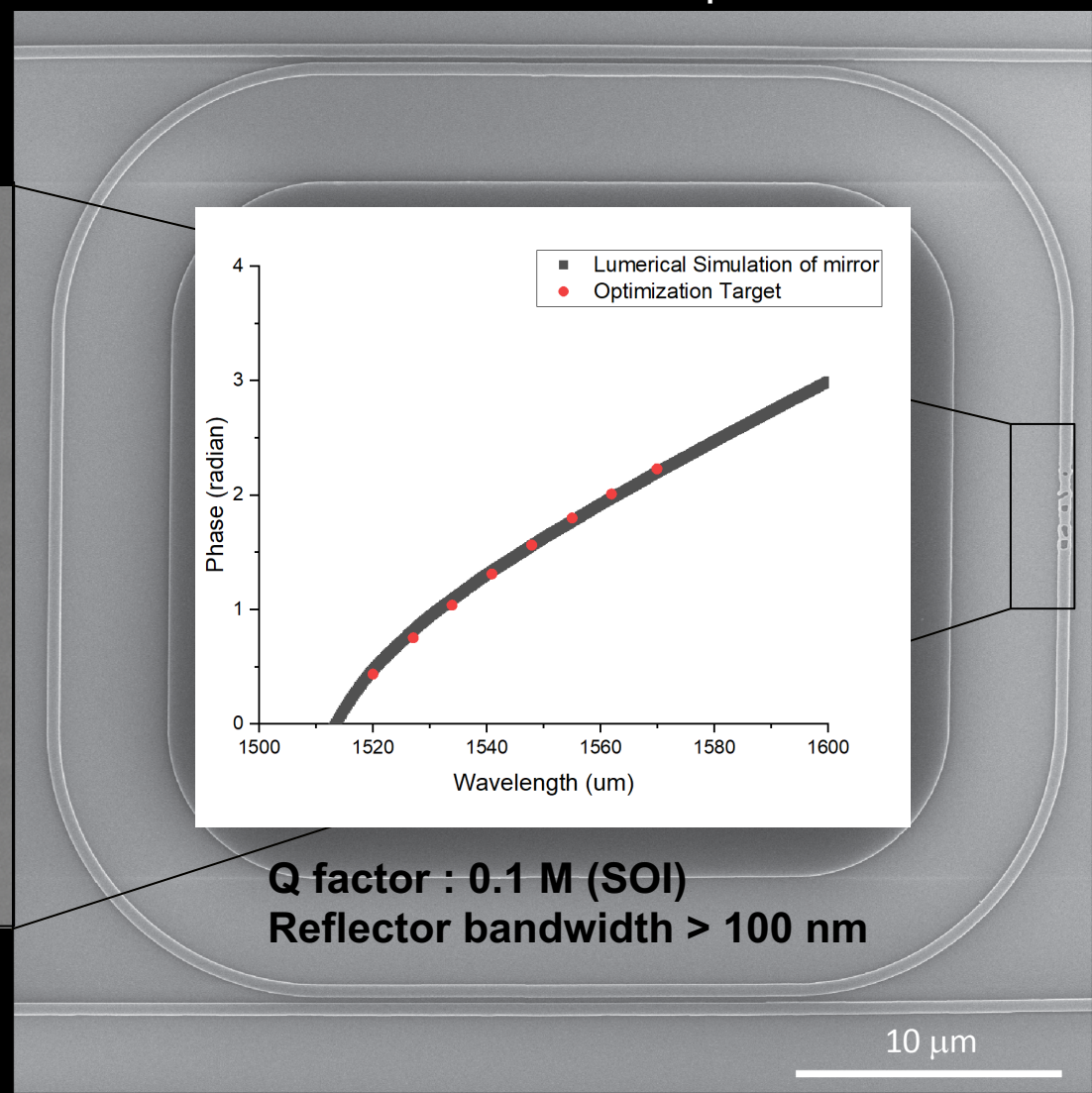
Douglas et al., *Nature Photonics* 9, 326–331 (2015).

R. Trivedi, S. Sun, in collaboration with I. Cirac, D. Lanz (MPQ)

Inverse design for dispersion engineering



Microresonator dispersion



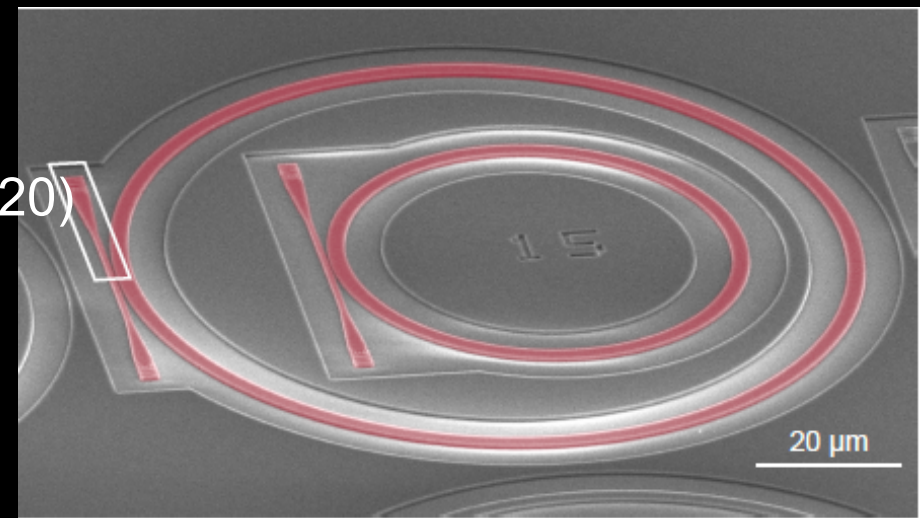
Dries Vercruyssen et al, IEEE JSTQE (2019)

- **4H silicon Carbide Quantum and nonlinear Photonics**

D. Lukin, C. Dory, M. Guidry et al, *Nature Photonics* **14**, 330–334 (2020)

D. Lukin, A. White, M. Guidry, R. Trivedi et al [*arXiv:2003.12591*]

M. Guidry, K. Yang, D. Lukin et al [*arXiv:2004.13958*]



- **SiV and SnV in inverse designed diamond cavities**

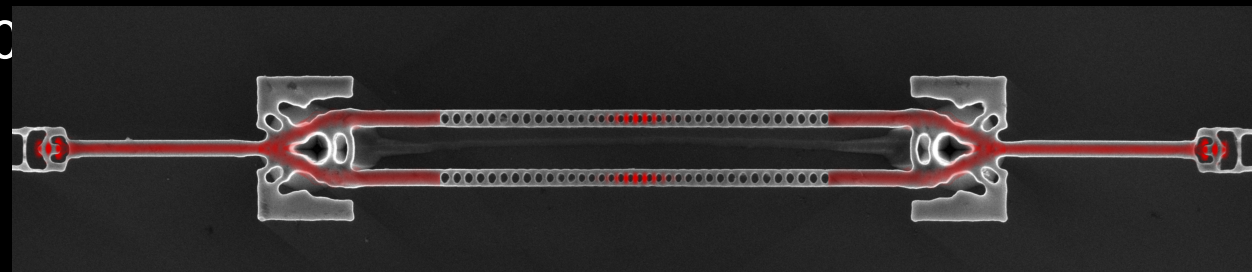
Shuo Sun et al, *Phys. Rev. Letters* **121**, 083601 (2018)

C. Dory, et al., *Nature Comm.* **10**, 3309 (2019)

A. Rugar, et al., *Phys. Rev. B* **99**, 205417 (2019),

Nano Letters **20**, 1614-1619 (2020)

[*arXiv:2005.10385*]

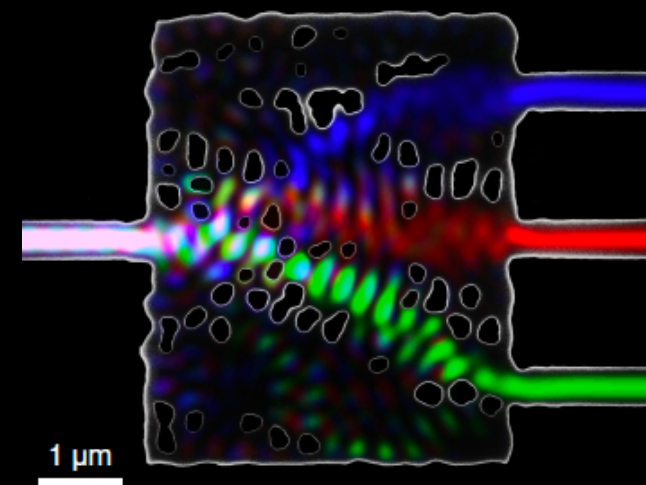


- **Photonics optimization critical for implementation of scalable and practical classical and quantum photonic systems**

Stanford Photonics **IN**verse design **S**oftware (**SPINS**), OTL S18-012

SPINS-B (open source) on Github <http://github.com/stanfordnqp/spins-b>

Fully compatible with foundry fabrication



Acknowledgement

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J. Bowers @ UCSB